

PIER Graduate Week 2017

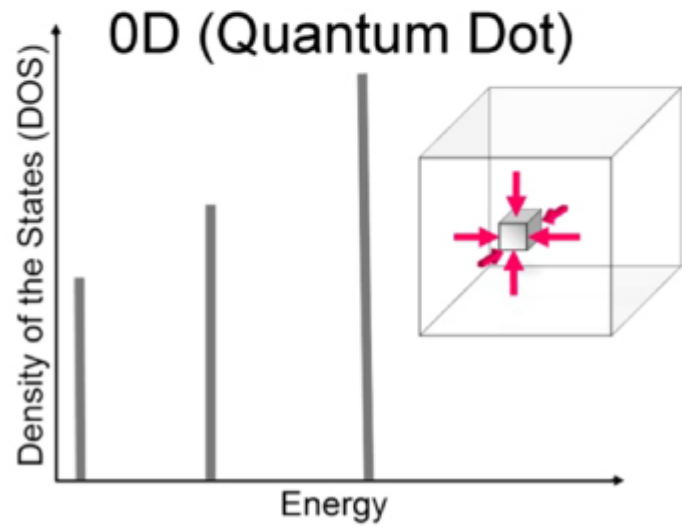
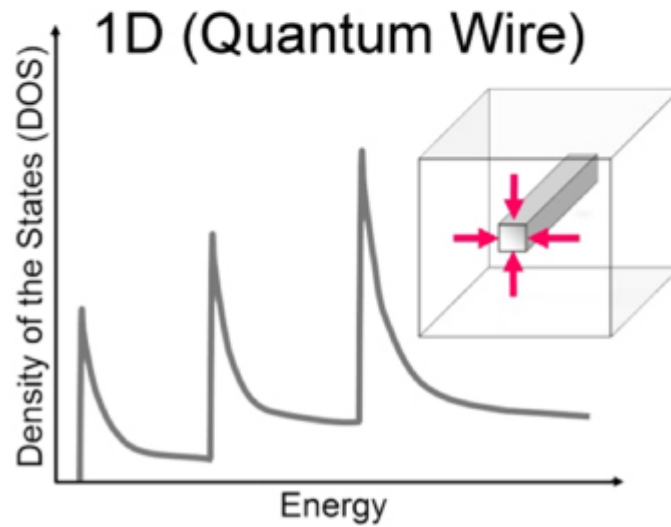
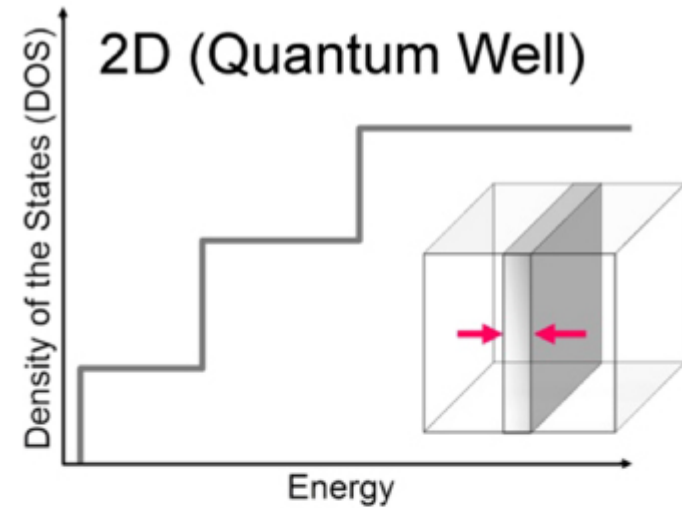
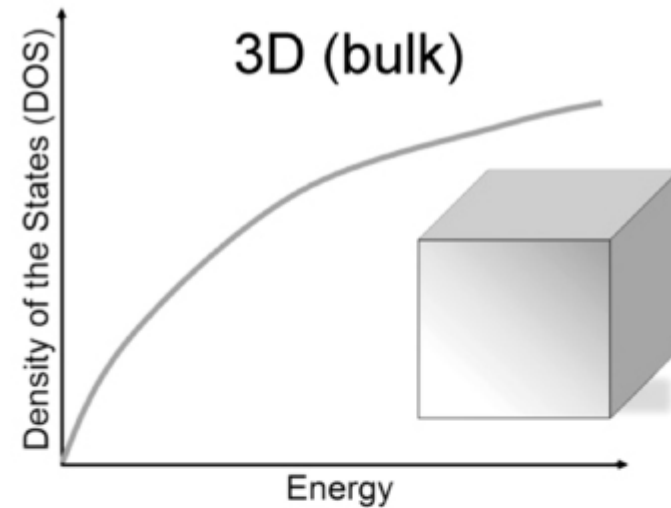
Nano-Optics of low dimensional semiconductor structures

Lecture 2: Nano-Optics of 2D Semiconductors

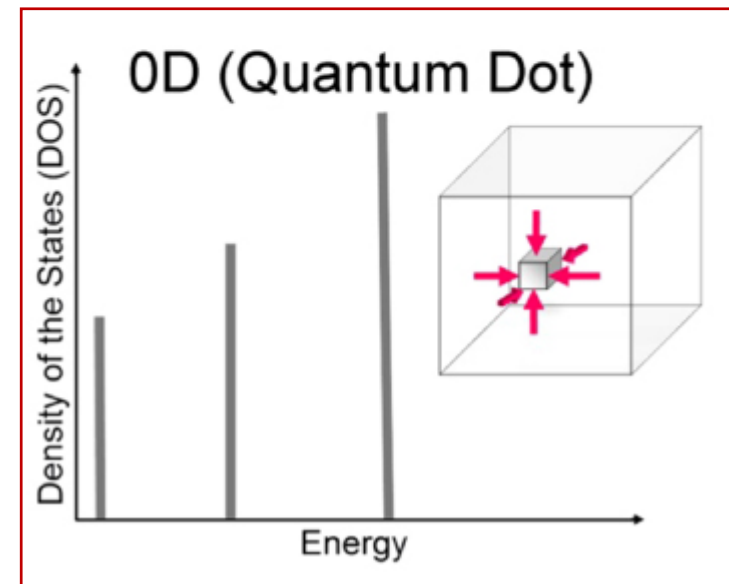
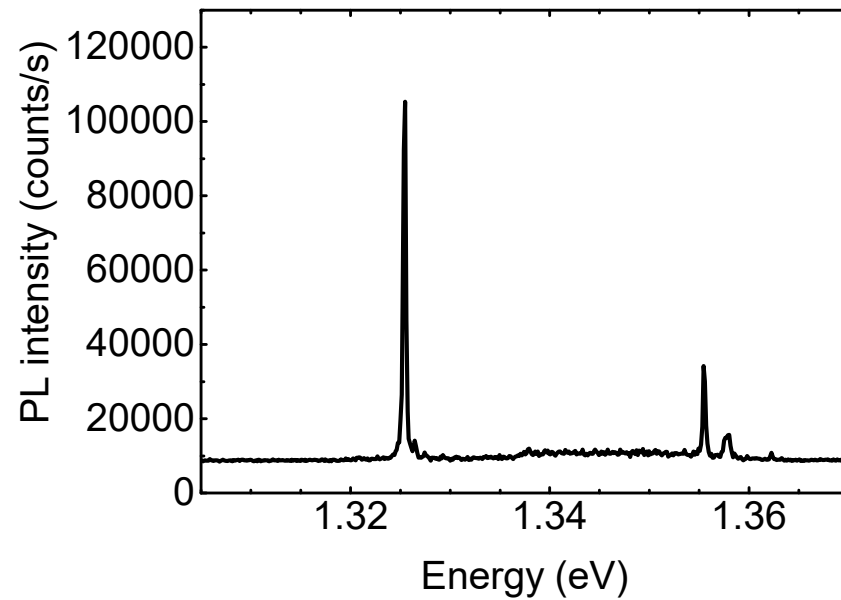
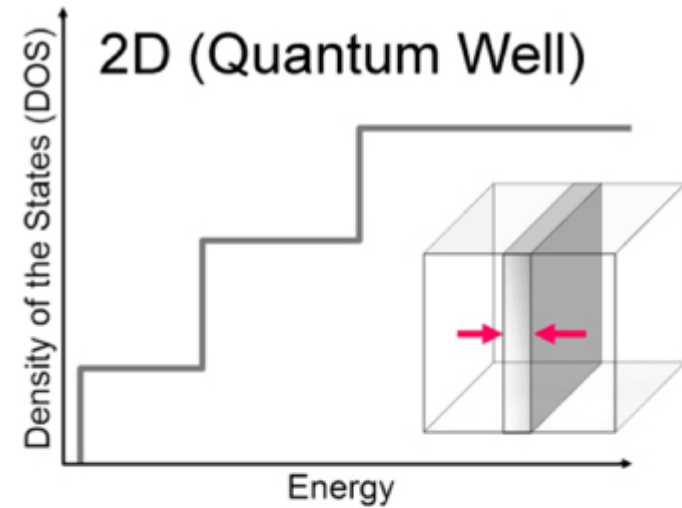
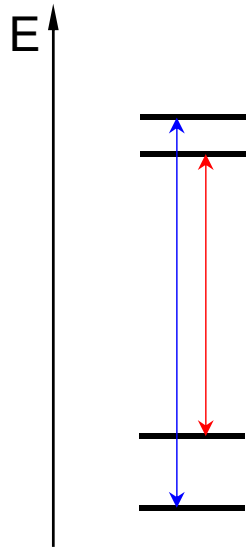
Martin Kroner

Quantum Photonics Group, ETH Zürich, Switzerland

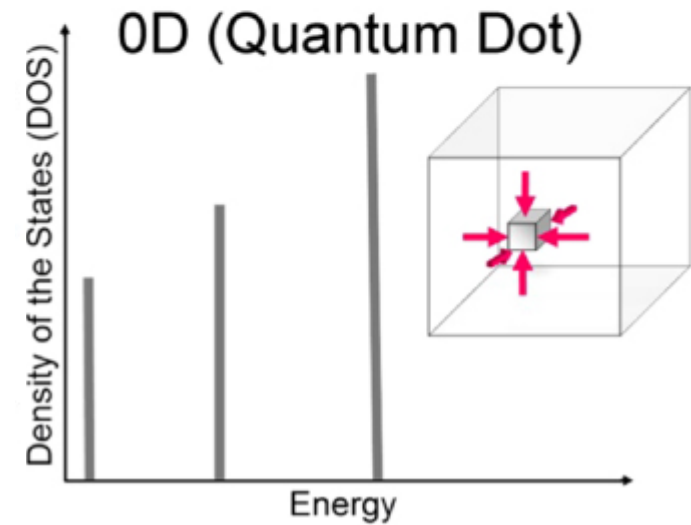
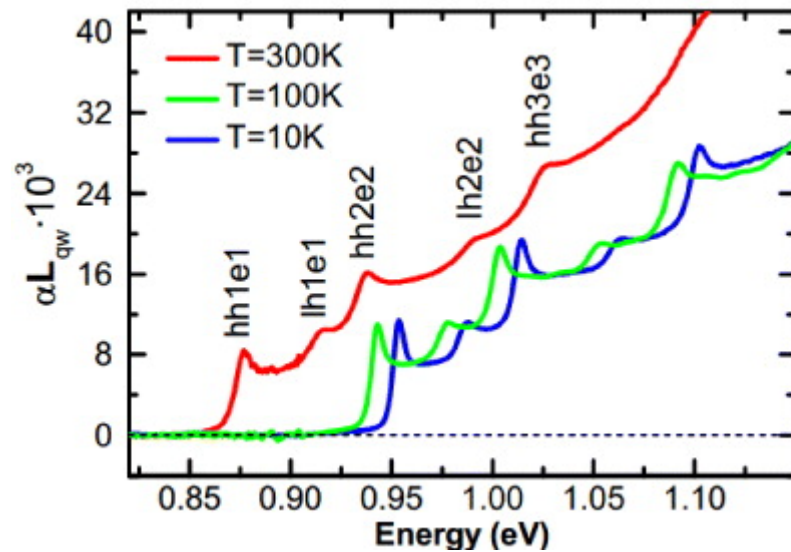
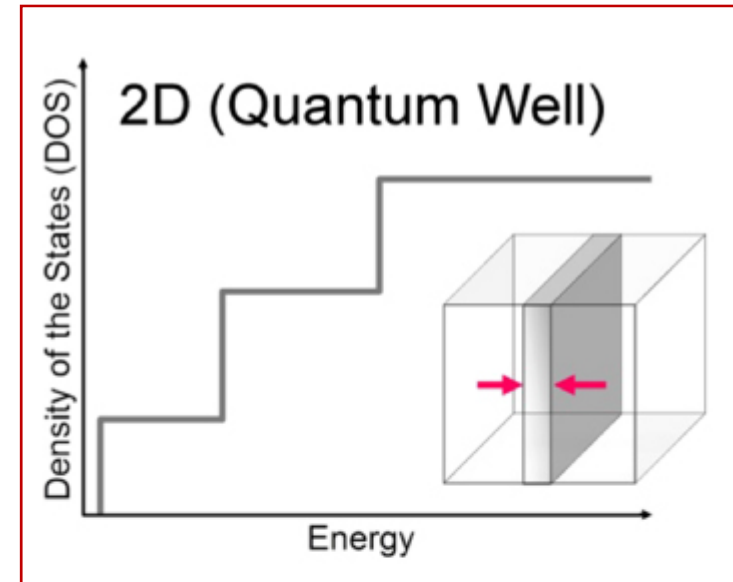
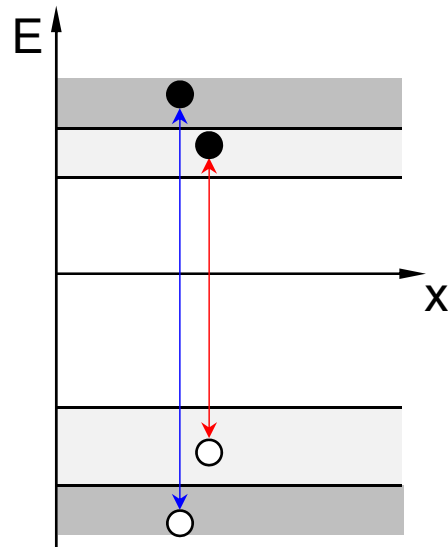
Dimensionality of optical systems



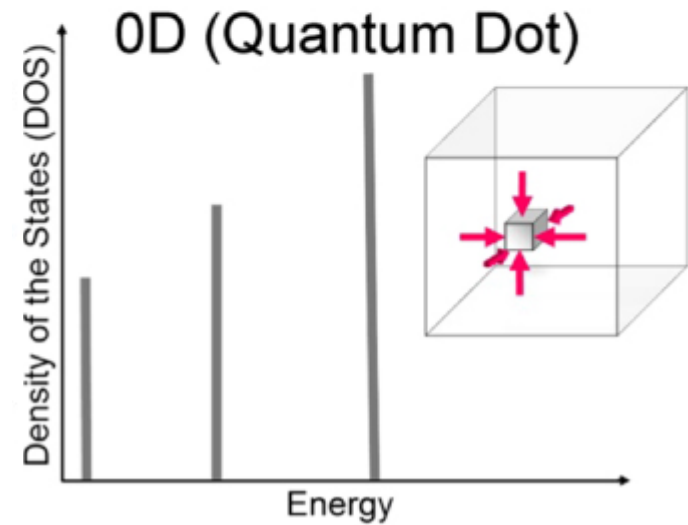
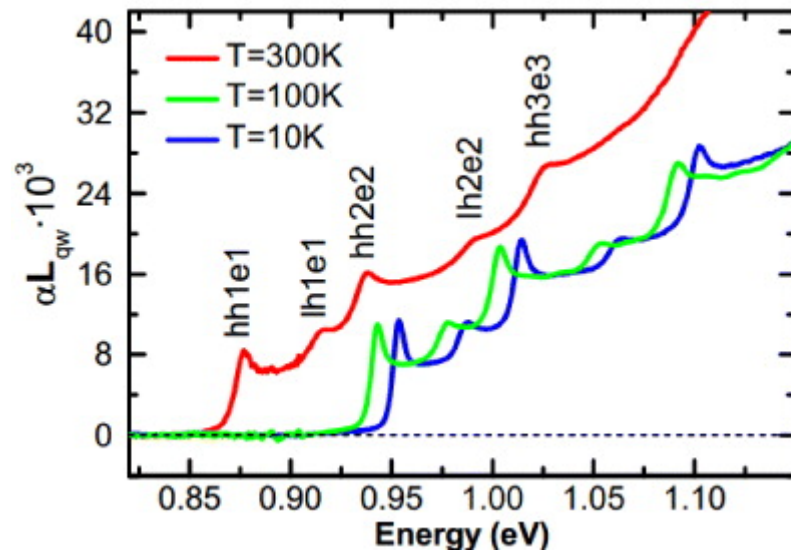
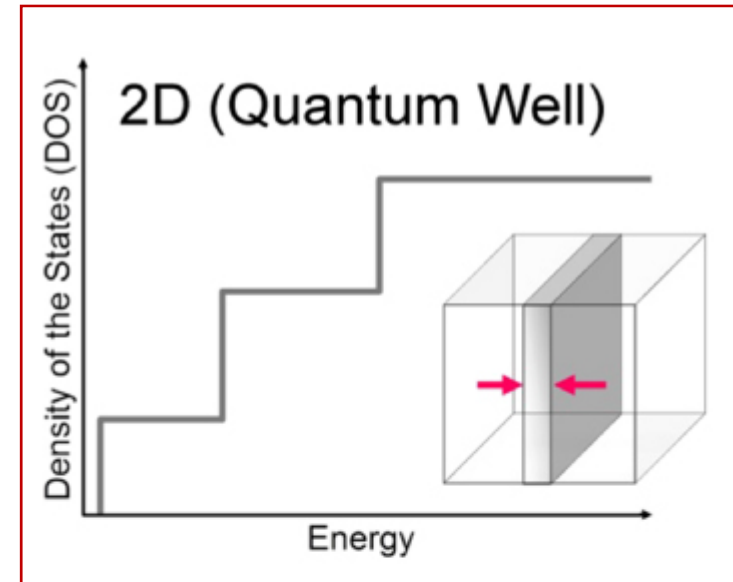
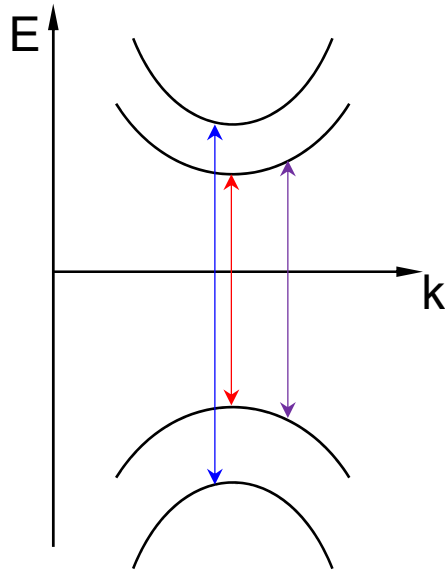
Optical Properties of a 0D System



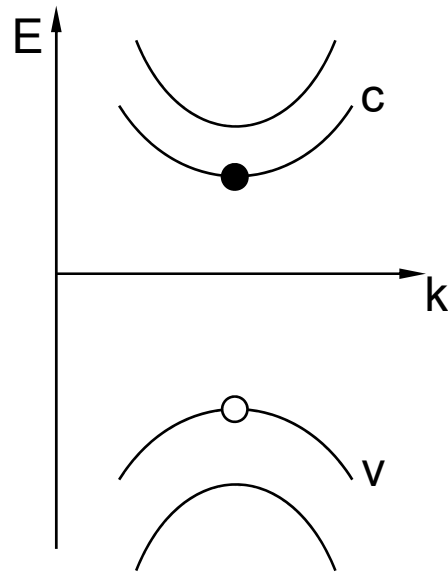
Optical Properties of a 2D System



Optical Properties of a 2D System



Excitons in 2D

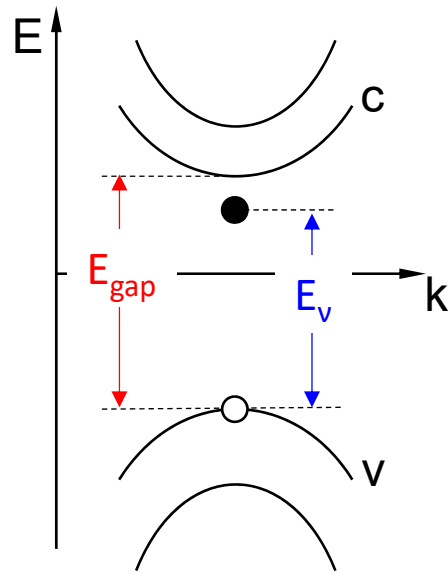


Electron and hole form bound state: Exciton

$$H_{\text{int}} \sim \int d^3r \int d^3r' \hat{\Psi}_s^\dagger(r) \hat{\Psi}_{s'}^\dagger(r') \frac{e^2}{|r-r'|} \hat{\Psi}_s(r) \hat{\Psi}_{s'}(r')$$

$$\hat{\Psi}_s(r) = \sum_{\mathbf{k}} (\psi_{c,\mathbf{k},s}(r) \hat{c}_{c,\mathbf{k},s} + \psi_{v,\mathbf{k},s}(r) \hat{c}_{v,\mathbf{k},s})$$

Excitons in 2D



i.e. in GaAs

$$E_{1s} - E_{\text{gap}} \approx 20 \text{ meV}$$

Electron and hole form bound state: Exciton

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...

$\Rightarrow$ Hydrogen like equation:

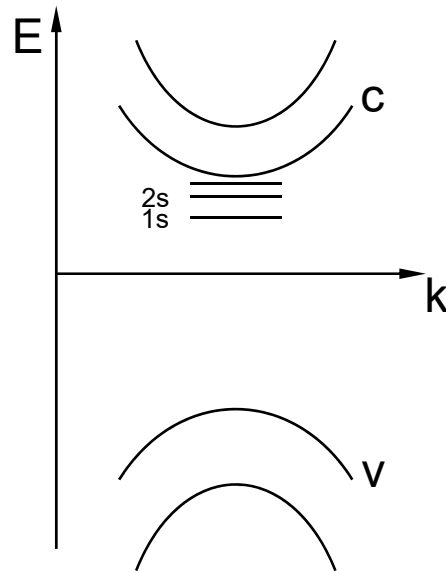
$$(E_\nu - E_{\text{gap}}) \tilde{\psi}_\nu(r) = \left(\frac{-\hbar^2 \nabla^2}{2m_r} - \frac{e^2}{\epsilon r} \right) \tilde{\psi}_\nu(r)$$

For different states: $\nu = 1s, 2s, 2p, \dots$

$$\text{i.e.: } \tilde{\psi}_{1s}(r) = \sqrt{\frac{8}{\pi}} \frac{1}{a_B} e^{\frac{-2r}{a_B}}$$

With the Bohr-radius $a_B = \frac{4\pi\epsilon_0\epsilon\hbar^2}{e^2 m_r}$

Excitons in 2D



Electron and hole form bound state: Exciton

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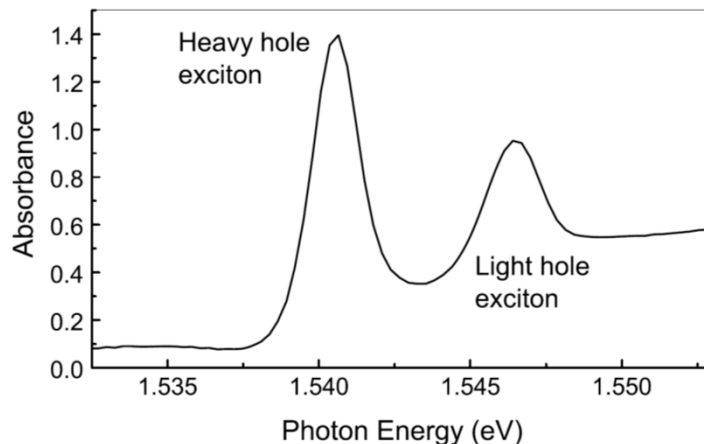
...

⇒ Hydrogen like equation:

$$(E_\nu - E_{\text{gap}}) \tilde{\psi}_\nu(r) = \left(\frac{-\hbar^2 \nabla^2}{2m_r} - \frac{e^2}{\epsilon r} \right) \tilde{\psi}_\nu(r)$$

i.e. in GaAs

$$E_{1s} - E_{\text{gap}} \approx 20 \text{ meV}$$



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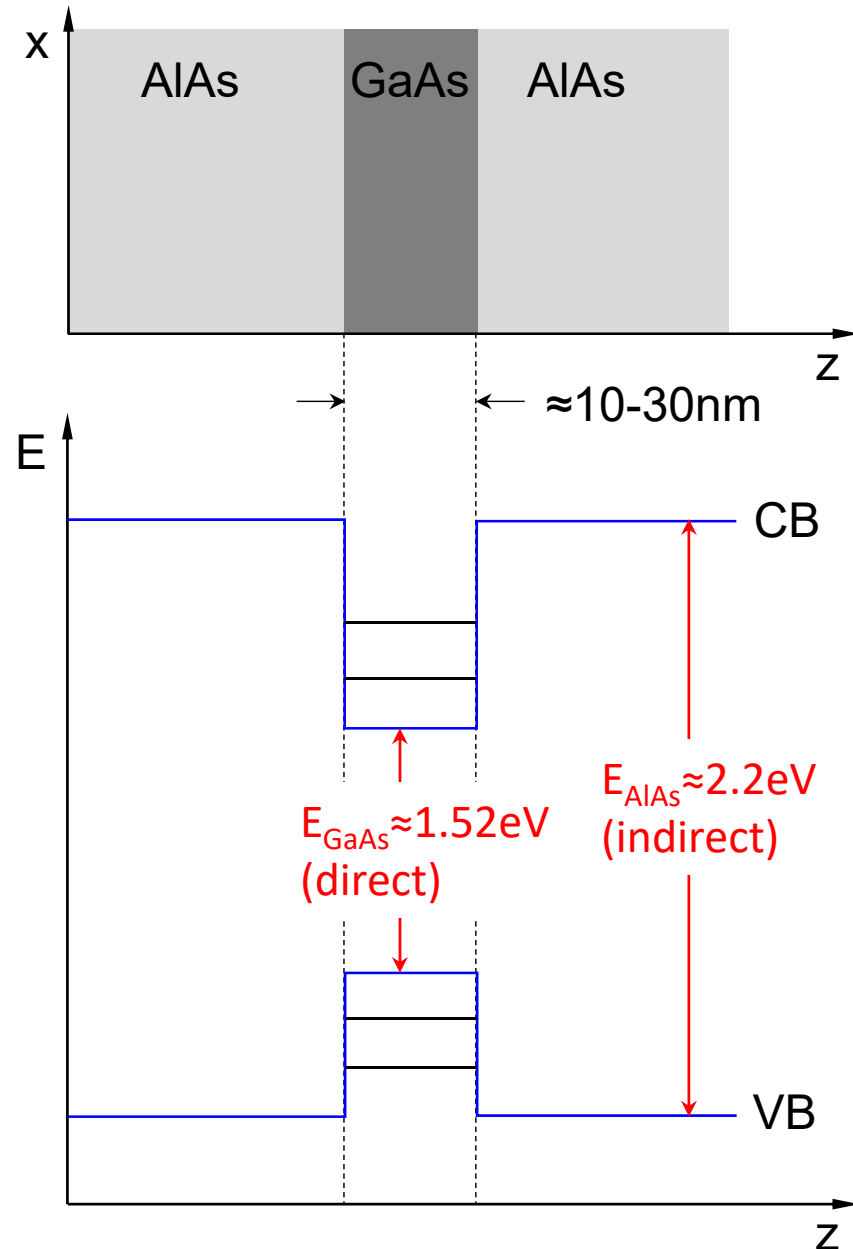
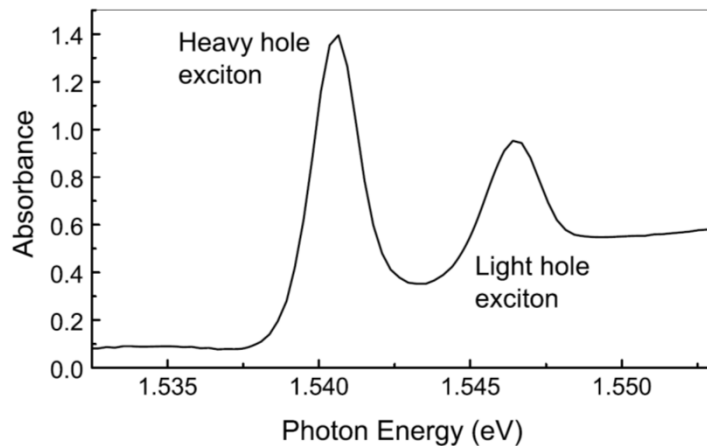
With the Bohr-radius $a_B = \frac{4\pi\epsilon_0\epsilon\hbar^2}{e^2 m_r}$

2D Semiconductors

Epitaxially grown heterostructures.

Material: III-V or II-VI

i.e. AlAs/GaAs quantum well



2D Semiconductors - Disorder

Epitaxially grown heterostructures.

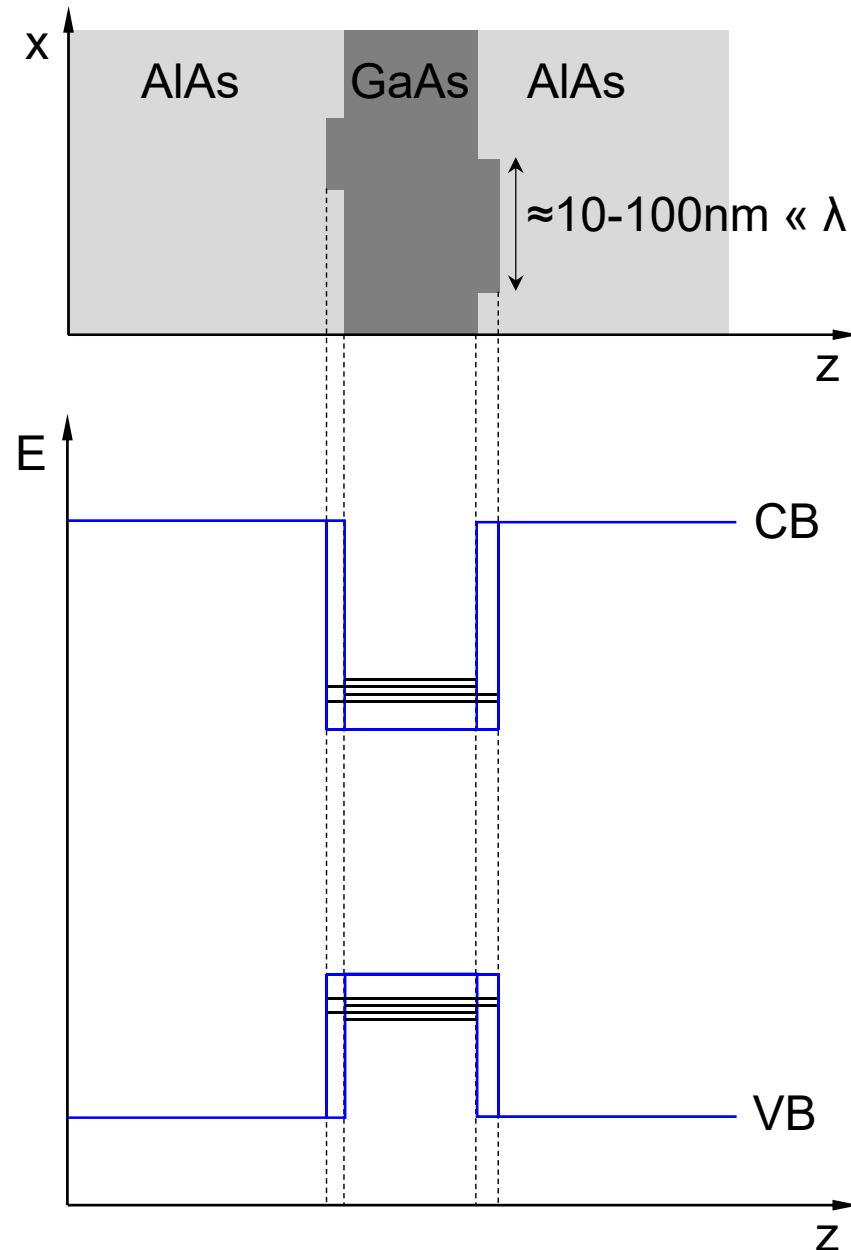
Few atom layer thickness variation

⇒ Several different exciton transition energies in a diffraction limited spot.

⇒ Inhomogeneous broadening of optical resonance.

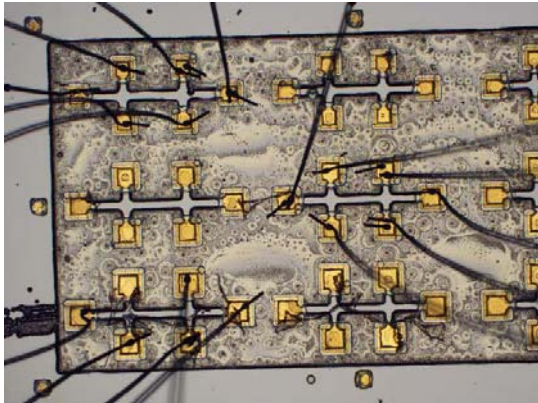
Homogeneous
(lifetime limited) line
width: $30\mu\text{eV}$

Typical measured
line width: $\sim 300\mu\text{eV}$

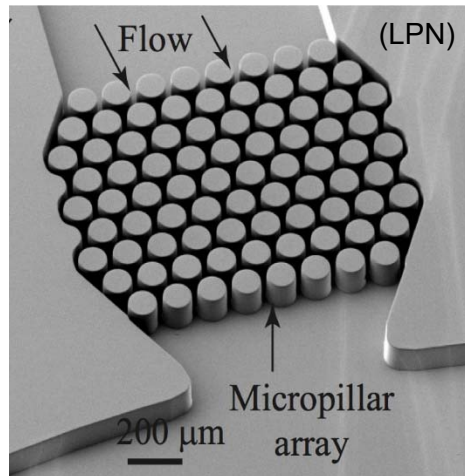


2D Semiconductor Technology

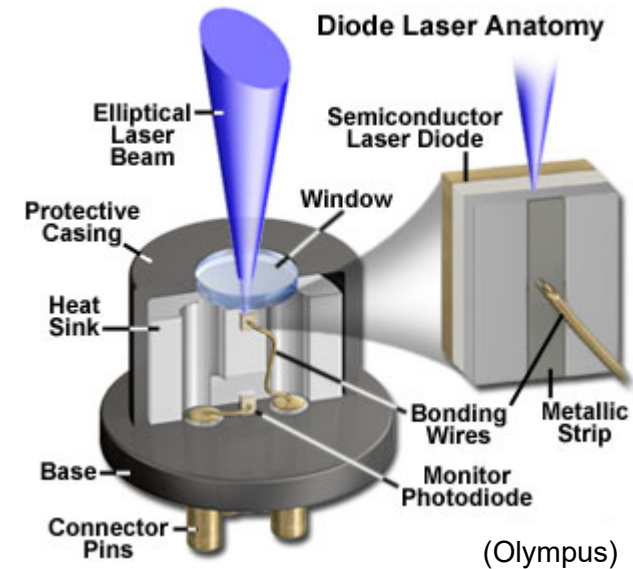
Electro optical devices



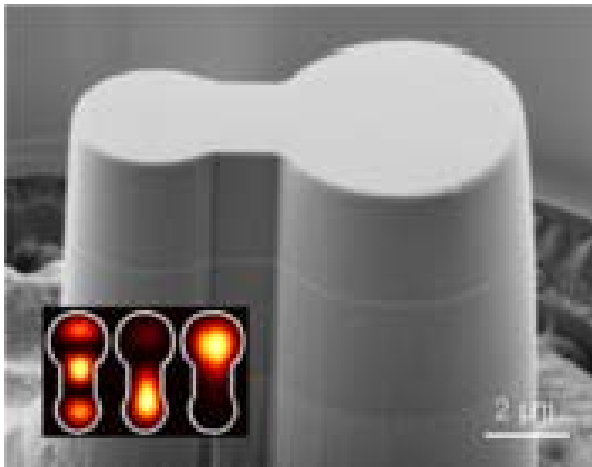
Hybrid devices



Laser diodes



Photonic devices



High quality material (optical and electrical properties)

Sophisticated growth and processing techniques

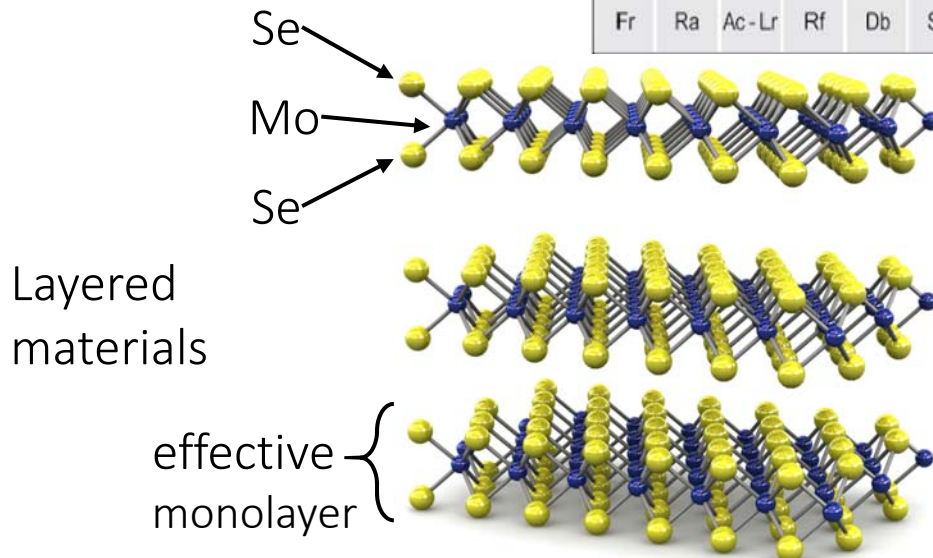
A New Type of 2D Semiconductors

Transition metal dichalcogenides (TMD):
A new class of truly two dimensional semiconductors

Formula: MX_2
M = Transition metal
X = Chalcogen

H																	He
Li	Be											B	C	N	O	F	Ne
Na	Mg	3	4	5	6	7	8	9	10	11	12	Al	Si	P	S	Cl	Ar
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe
Cs	Ba	La-Lu	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn
Fr	Ra	Ac-Lr	Rf	Db	Sg	Bh	Hs	Mt	Ds	Rg	Cn	Uut	Fl	Uup	Lv	Uus	Uuo

MX_2
M = Transition metal
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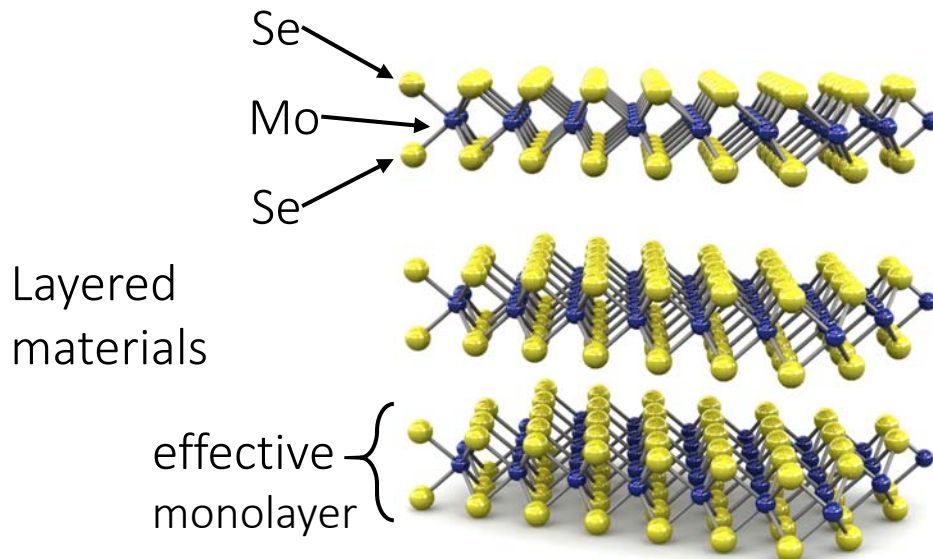


Electrical property	Material
Semiconducting	MoS_2 $MoSe_2$ WS_2 WSe_2 $MoTe_2$ WTe_2
Semimetallic	TiS_2 $TiSe_2$
Metallic, Superconducting	$NbSe_2$ NbS_2 $NbTe_2$ TaS_2 $TaSe_2$ $TaTe_2$

A New Type of 2D Semiconductors

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Metallic, CDW, Superconducting	NbSe ₂ NbS ₂ NbTe ₂ TaS ₂ TaSe ₂ TaTe ₂

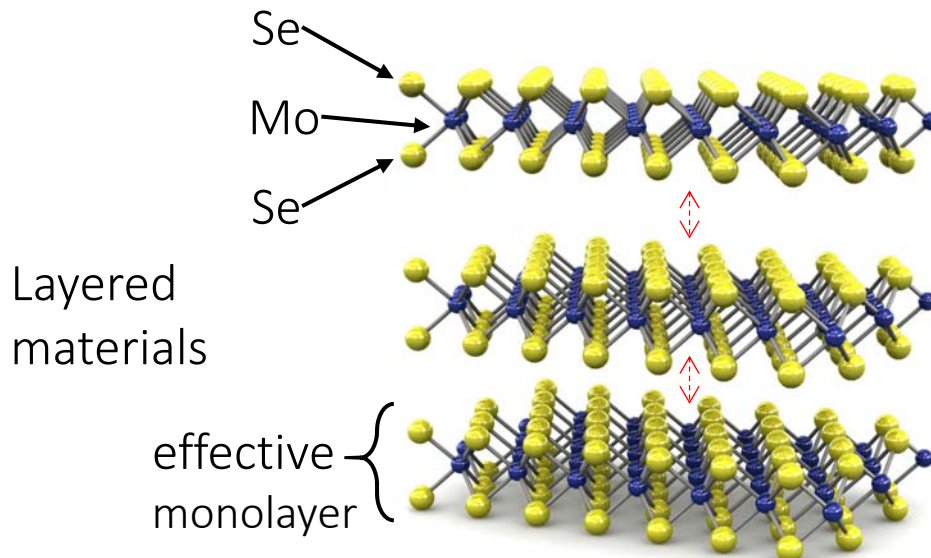
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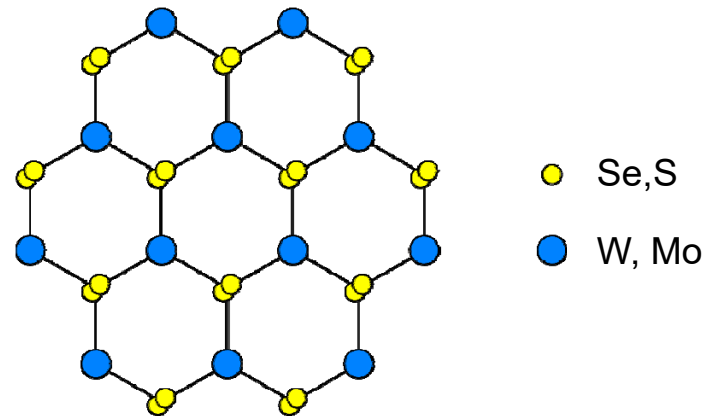
X = Chalcogen



Van der Waals bonds between layers
⇒ Single layers obtained by exfoliation

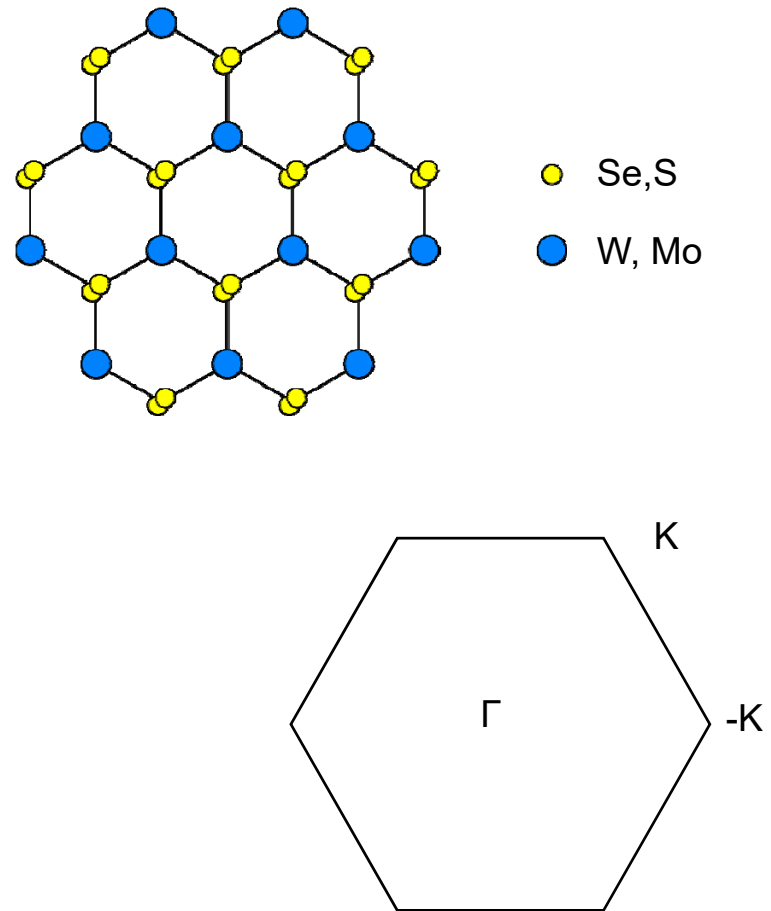
TMD Crystal Structure

- Monolayer has a honeycomb lattice



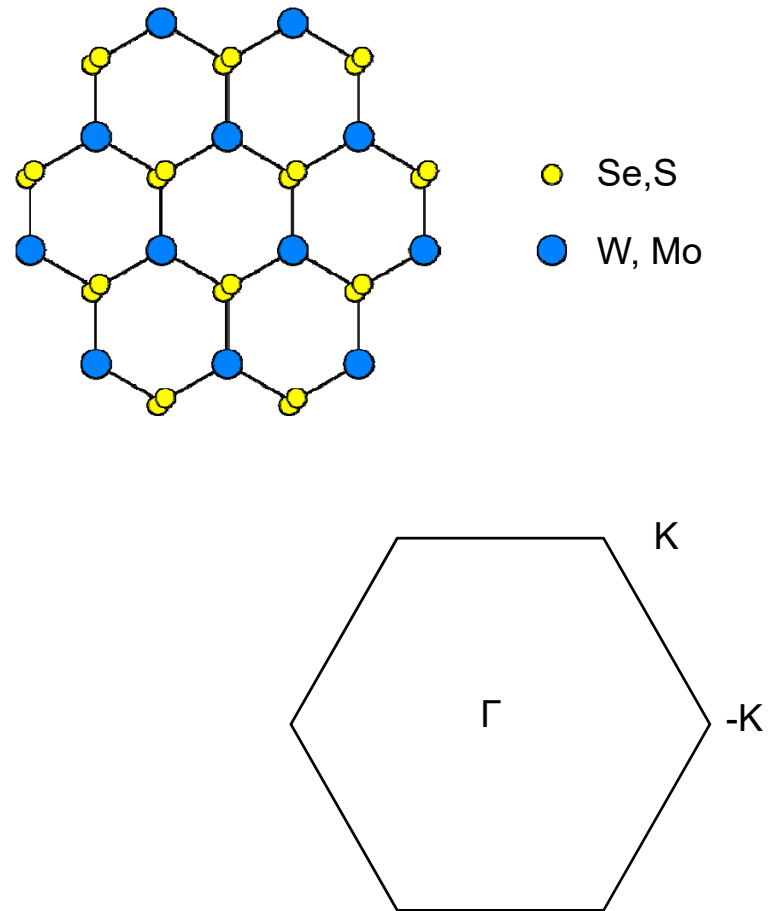
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TMD Crystal Structure

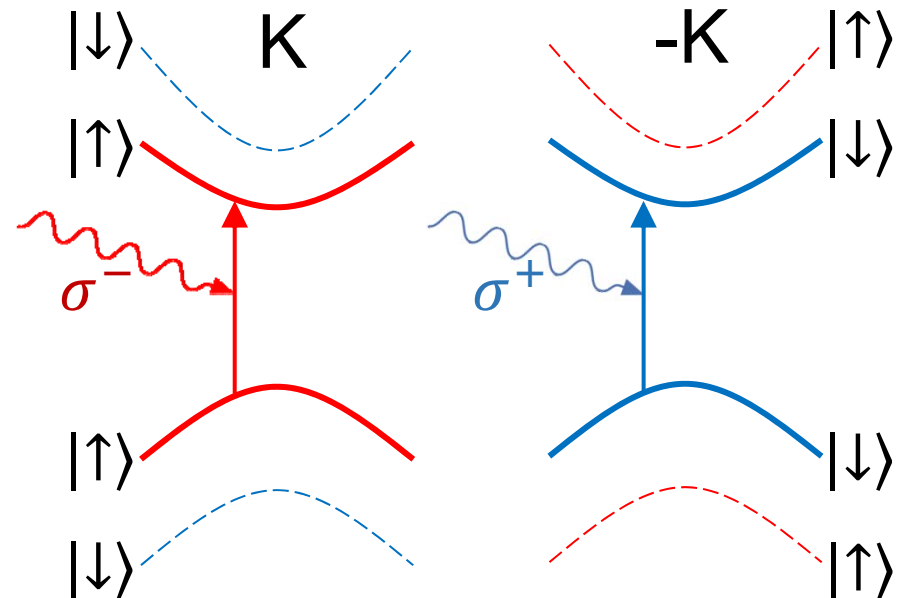
- Monolayer has a honeycomb lattice
- Valley semiconductor: physics at $\pm K$
- Broken inversion symmetry
→ band gap



Optical Addressing of Valleys in MoSe₂

$\pm K$ valleys respond to $\pm\sigma$ polarized light
 $\Rightarrow$ valley addressability like spin

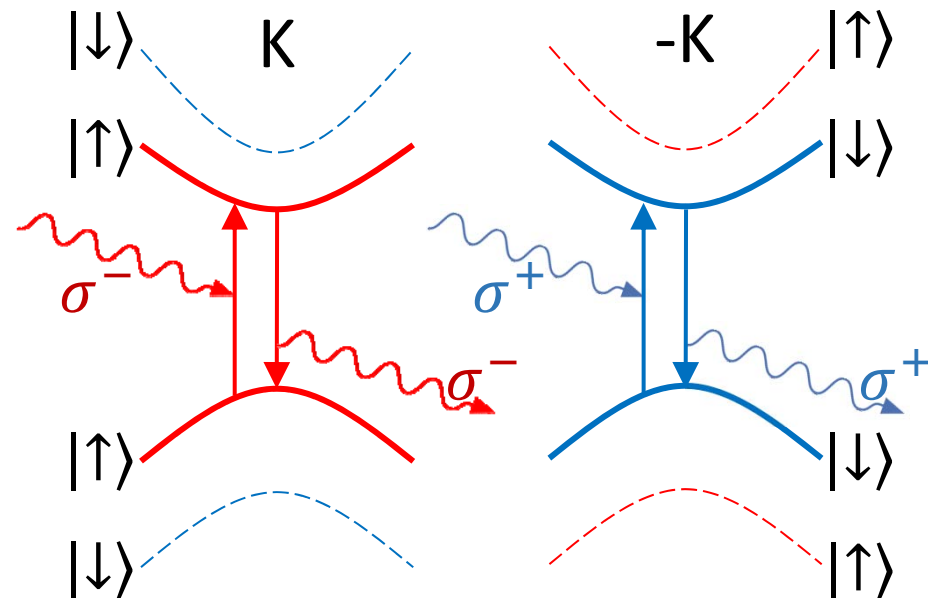
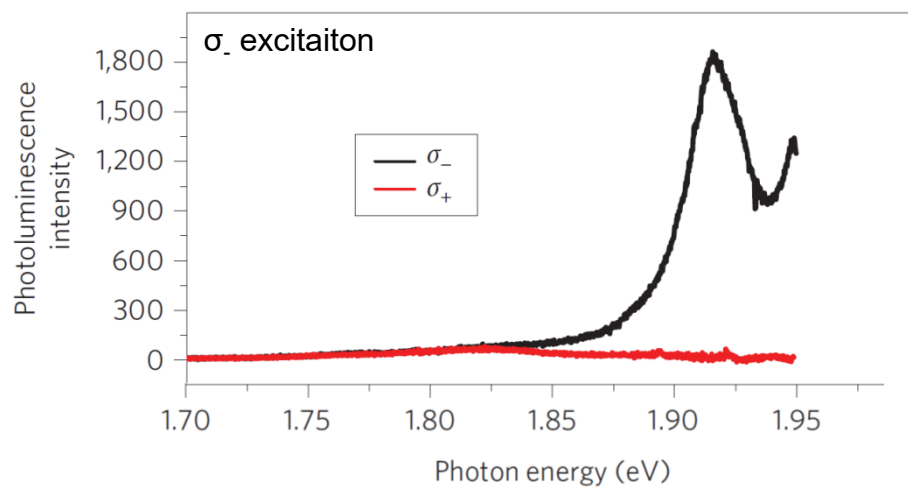
protection of spin coherence due to spin-valley locking?



Optical Addressing of Valleys in MoSe₂

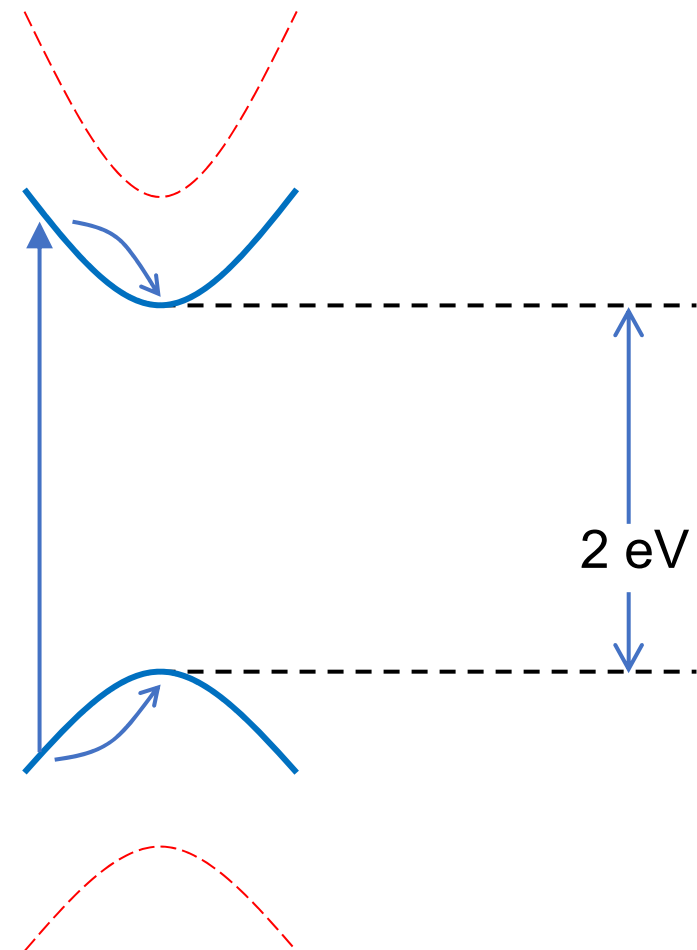
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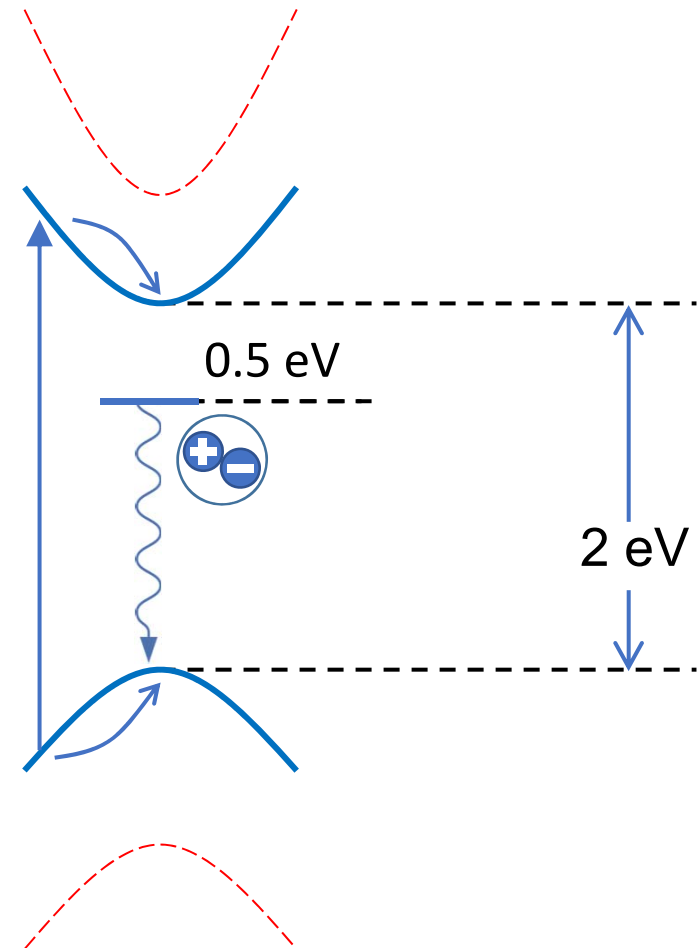
Photoluminescence of TMD Monolayers

- Excitation of high-energy free electron-hole pairs
- Strong Coulomb interaction due to lack of screening (truly 2D)



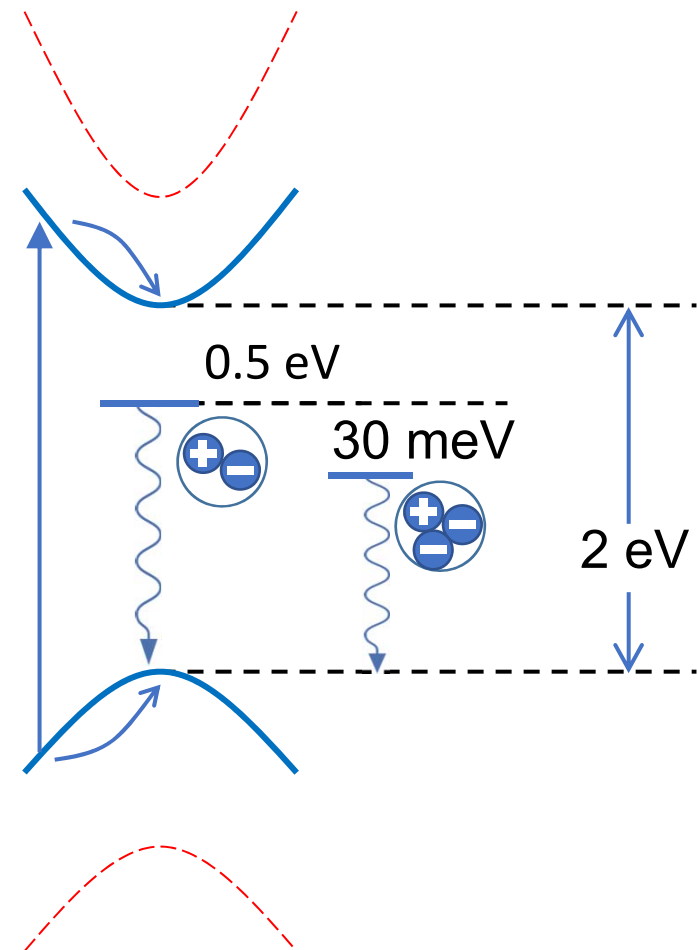
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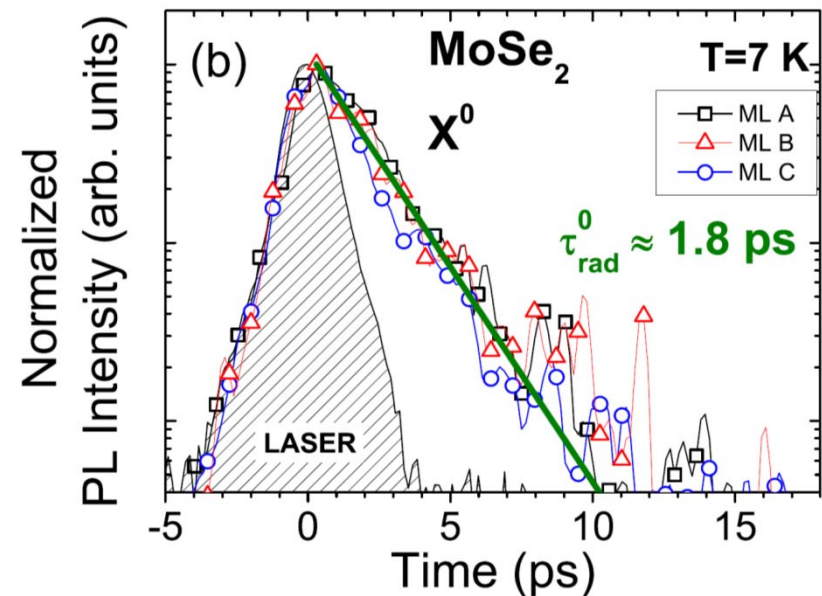
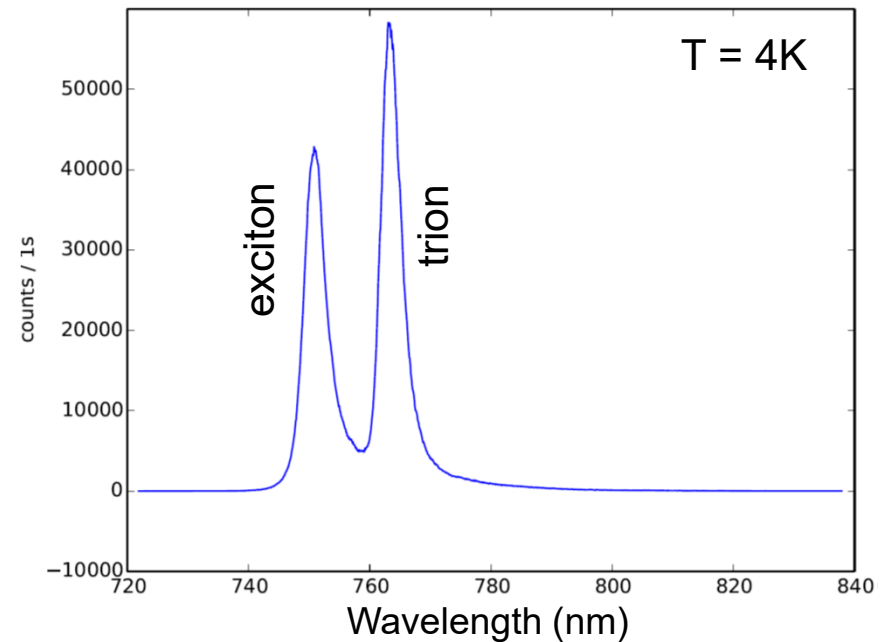
Photoluminescence of TMD Monolayers

- Excitation of high-energy free electron-hole pairs
- Strong Coulomb interaction due to lack of screening (truly 2D)
- Excitons form with huge binding energy of 500 meV
- PL is dominated by decay from exciton and trion



Photoluminescence of TMD Monolayers

- PL dominated by exciton and trion peaks
- Most flakes are electron doped hence the trion peak
- Smallest linewidth:
 $\Delta E = 3 \text{ meV}$
- Radiative lifetime:
 $\Gamma_{\text{rad}} \geq 1 \text{ meV}$
- Small exciton Bohr radius $\rightarrow$ strong light-matter coupling



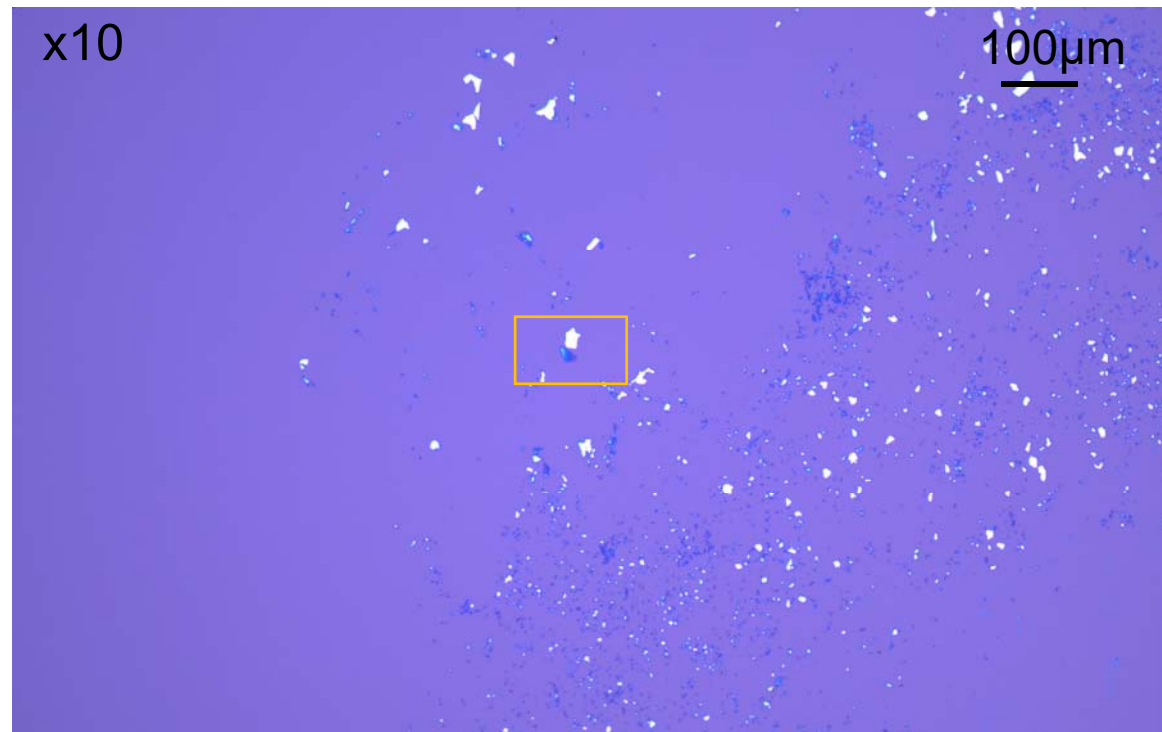
Van-der Waals Heterostructure

Exfoliation (and finding) of a monolayer: Optical microscopy image



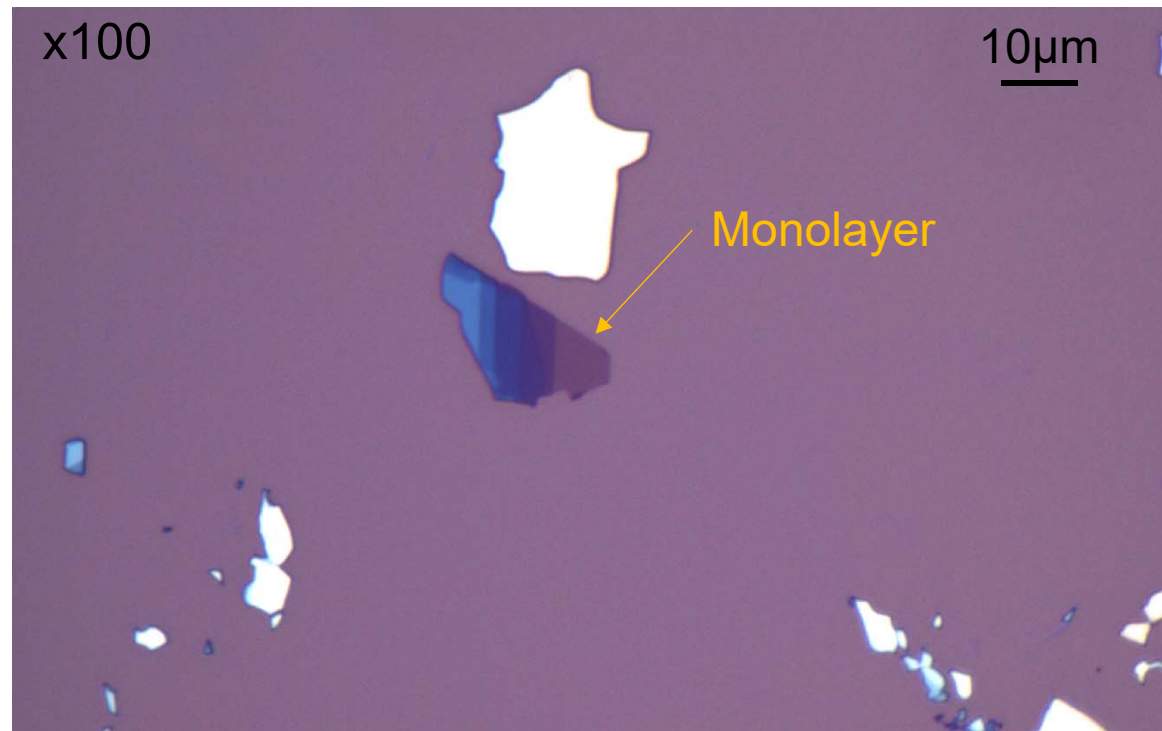
Van der Waals Heterostructure

Exfoliation (and finding) of a monolayer: Optical microscopy image



Van der Waals Heterostructure

Exfoliation (and finding) of a monolayer: Optical microscopy image

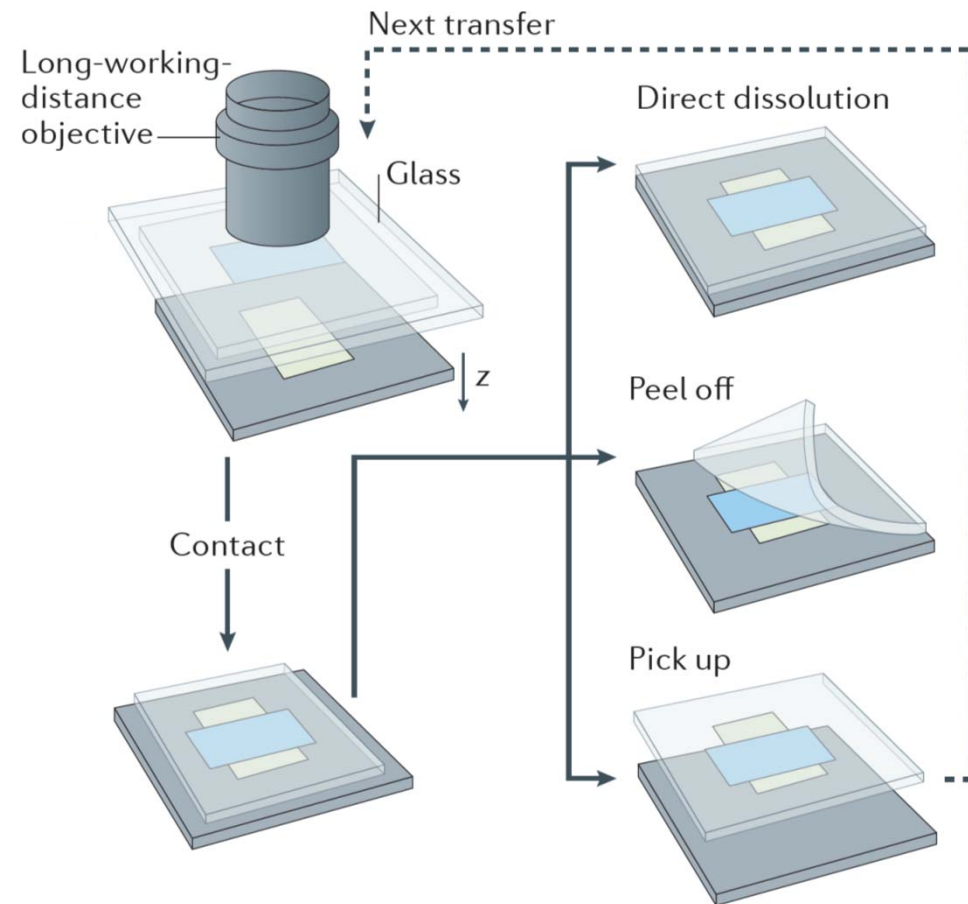
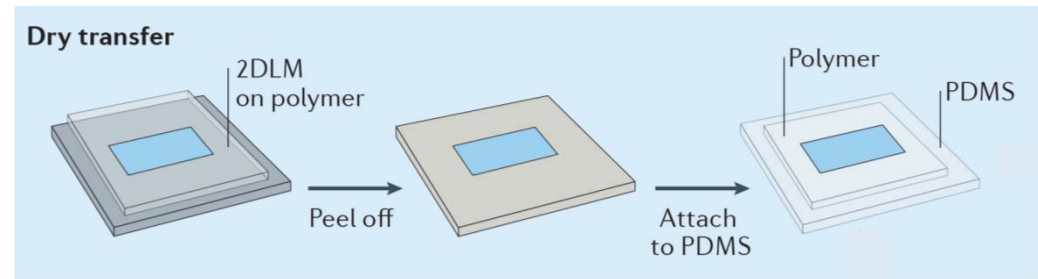
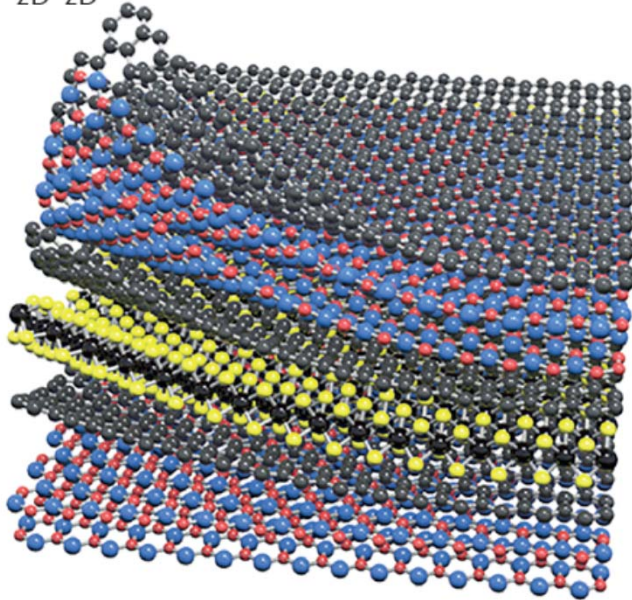


Van-der Waals Heterostructure

Exfoliation and dry pick-up and transfer

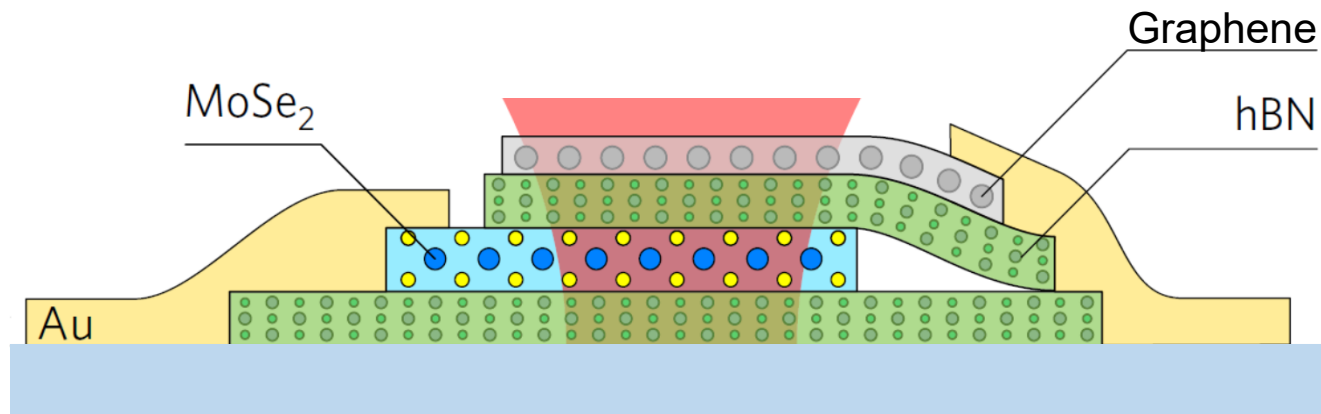
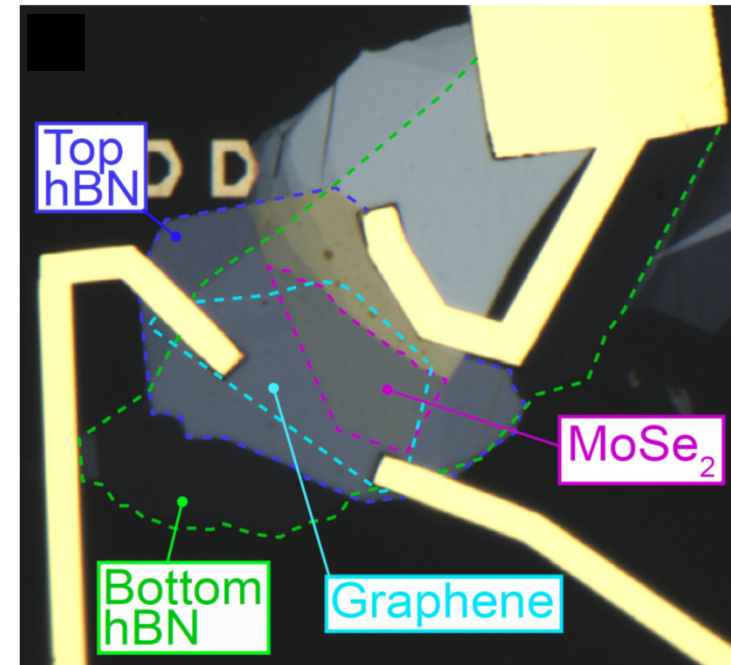
⇒ Build heterostructures

2D-2D



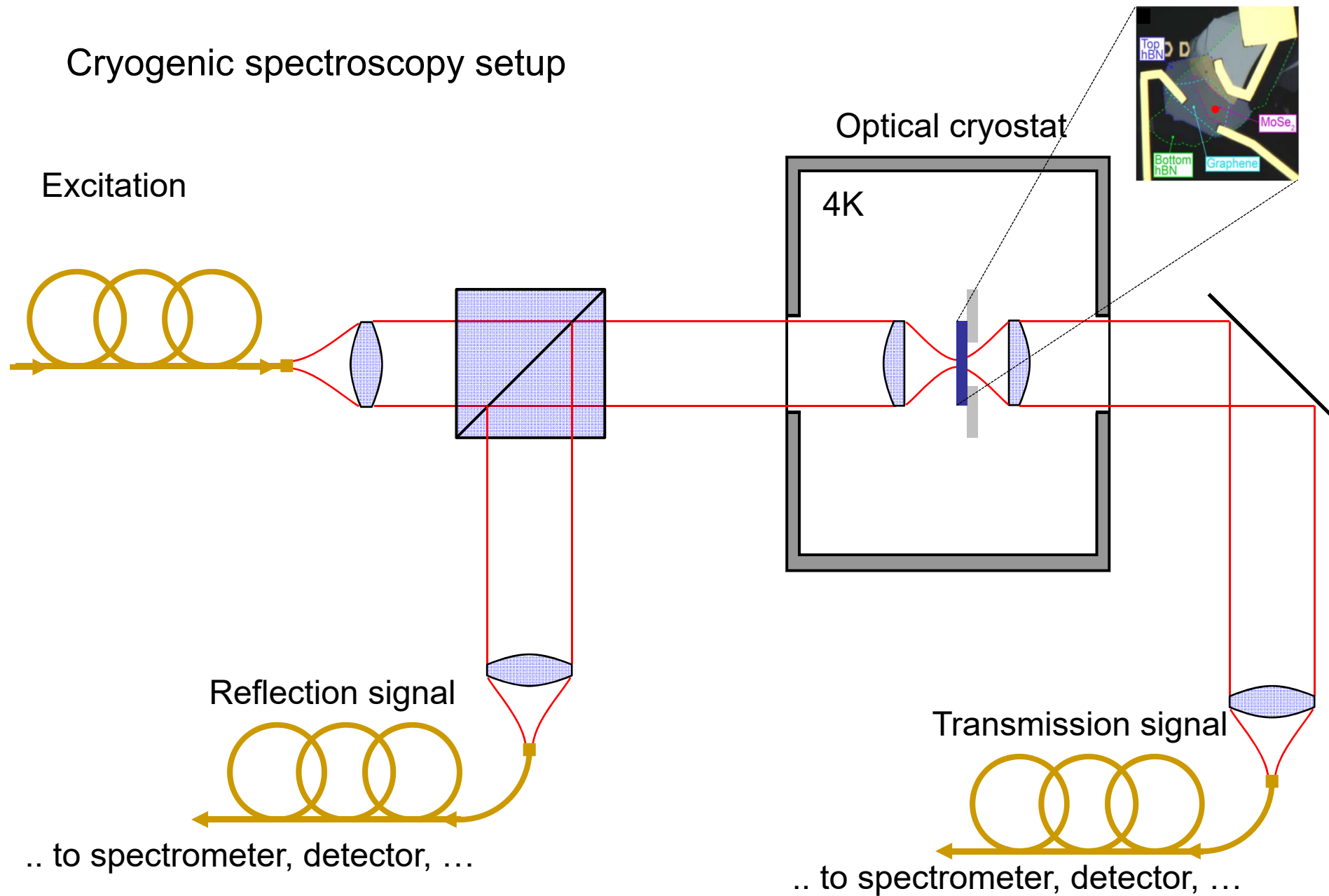
Van der Waals Heterostructure

- MoSe_2 monolayer
- Encapsulated in hBN
 - $\Rightarrow$ Match crystal structure
 - Protect against contamination
- Graphene gate electrode
 - $\Rightarrow$ Control electron density

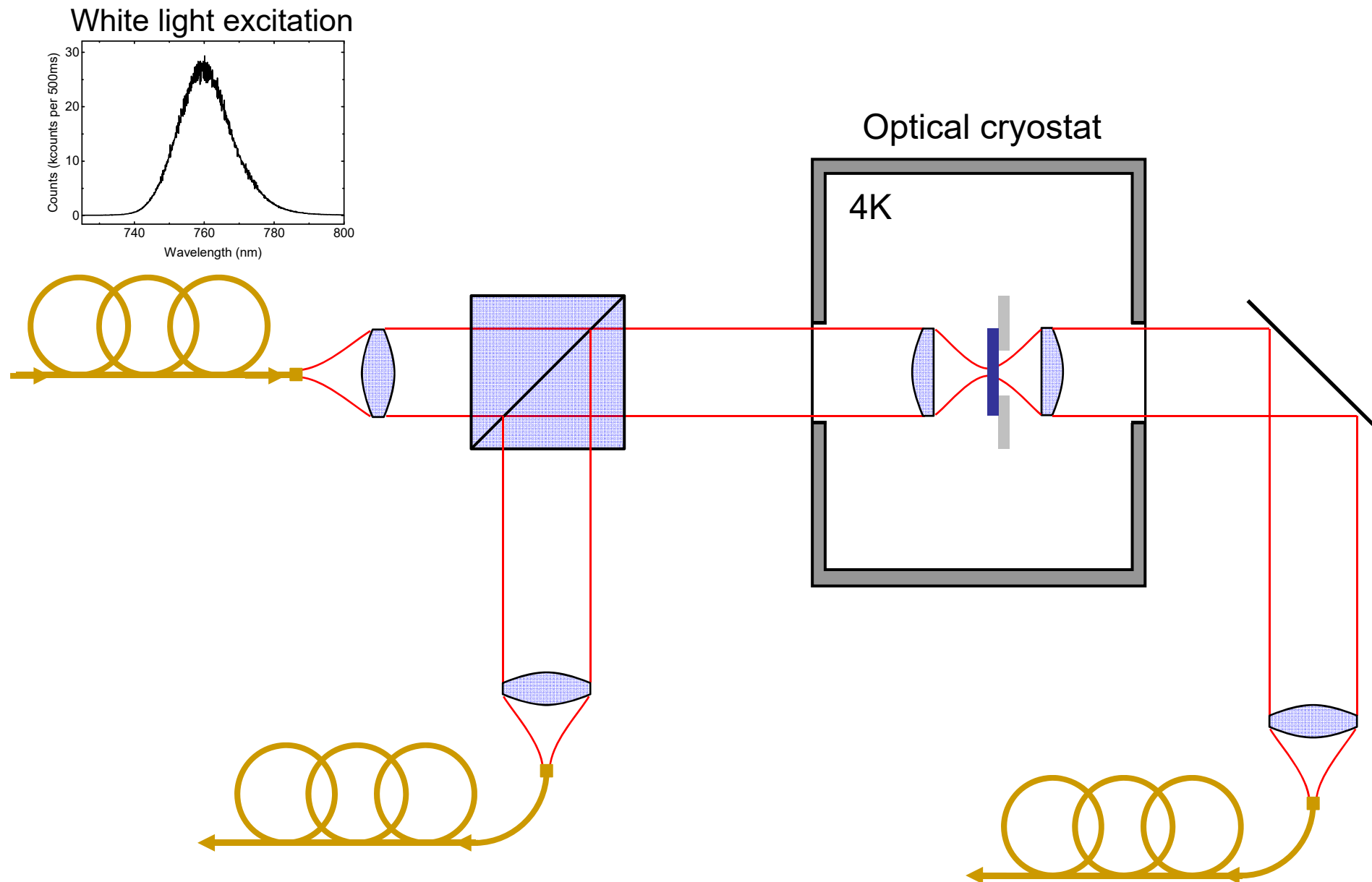


Reflection and Transmission Spectroscopy

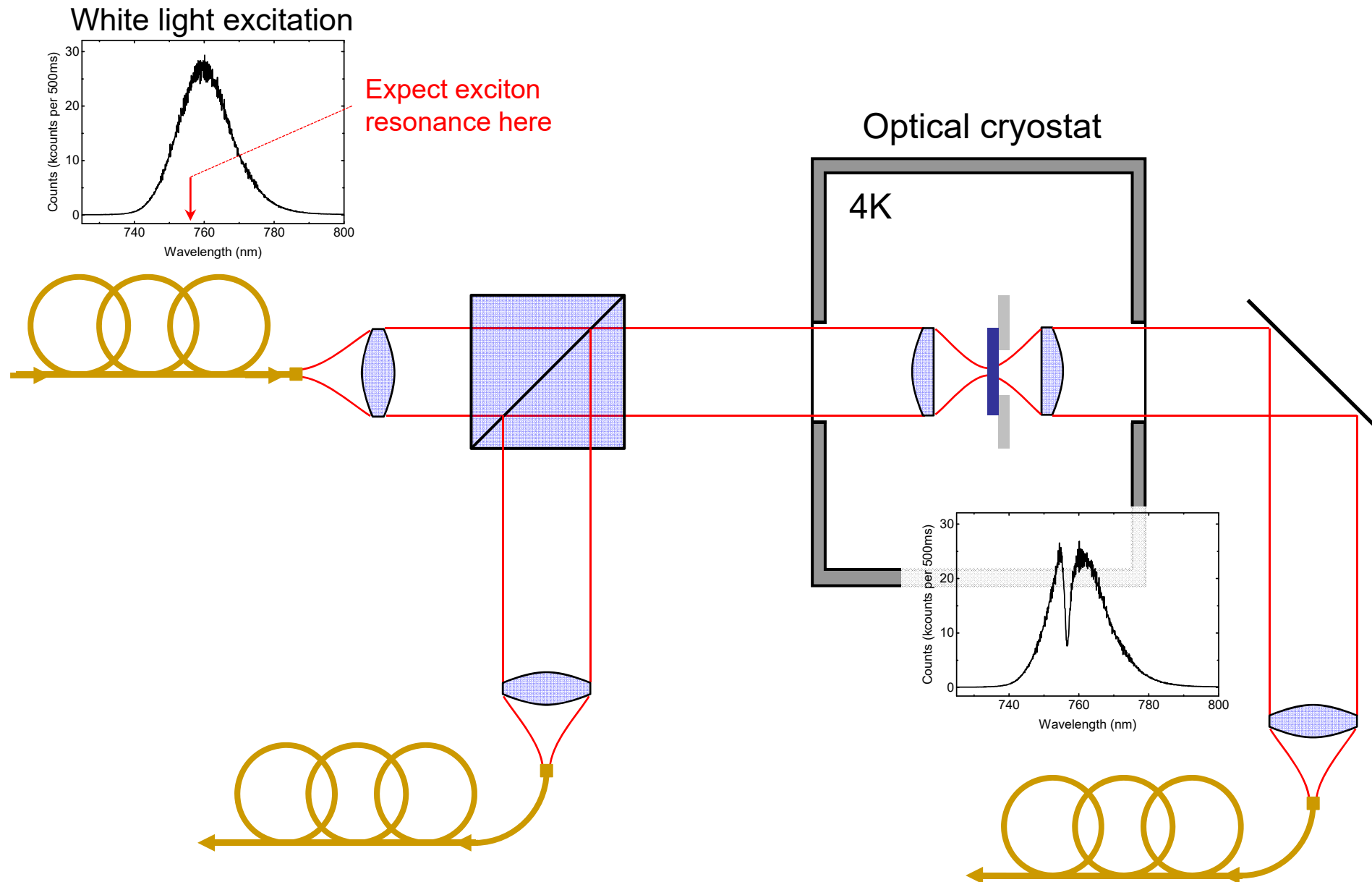
Cryogenic spectroscopy setup



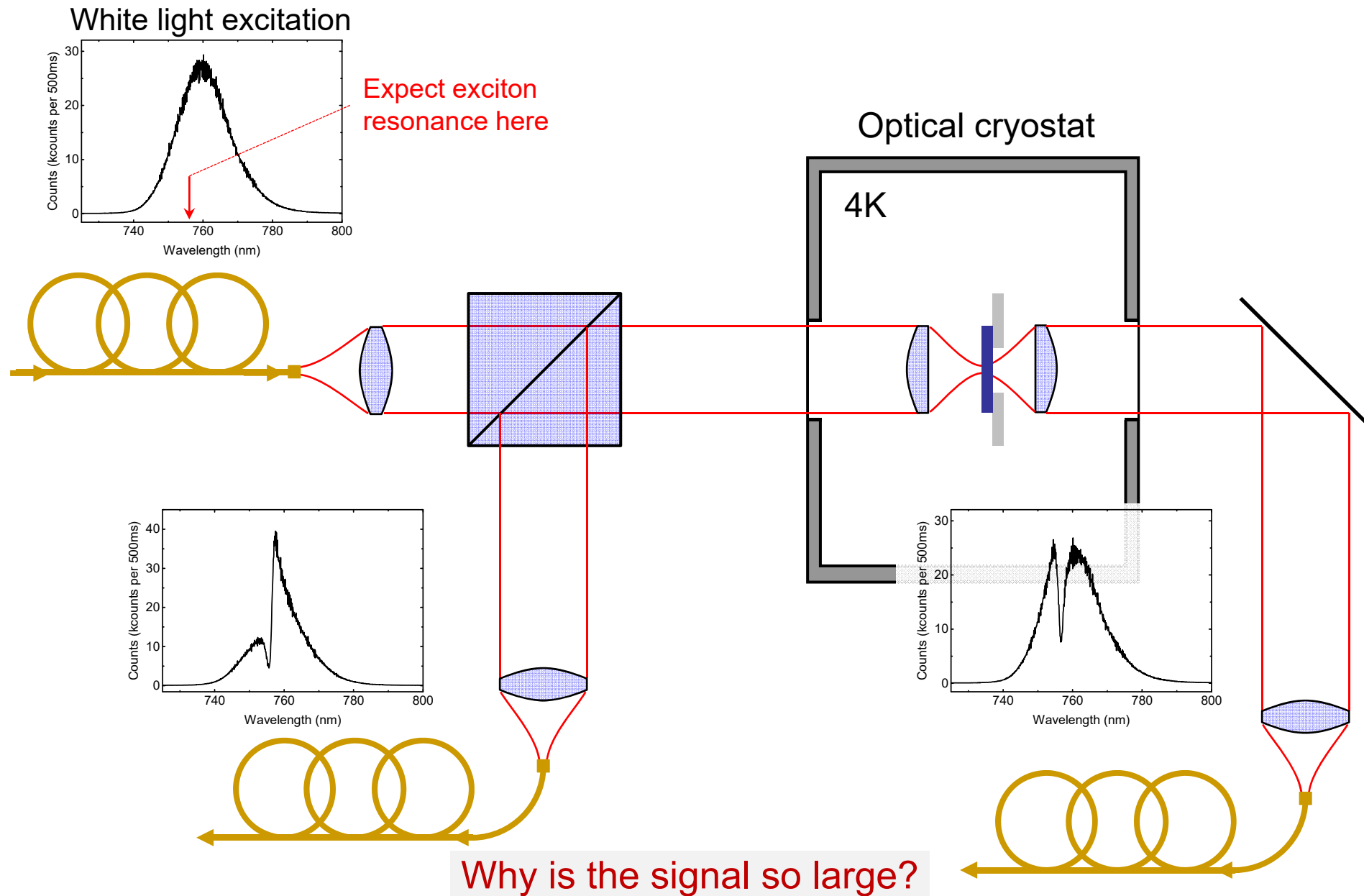
Optical Response of a MoSe₂ Monolayer



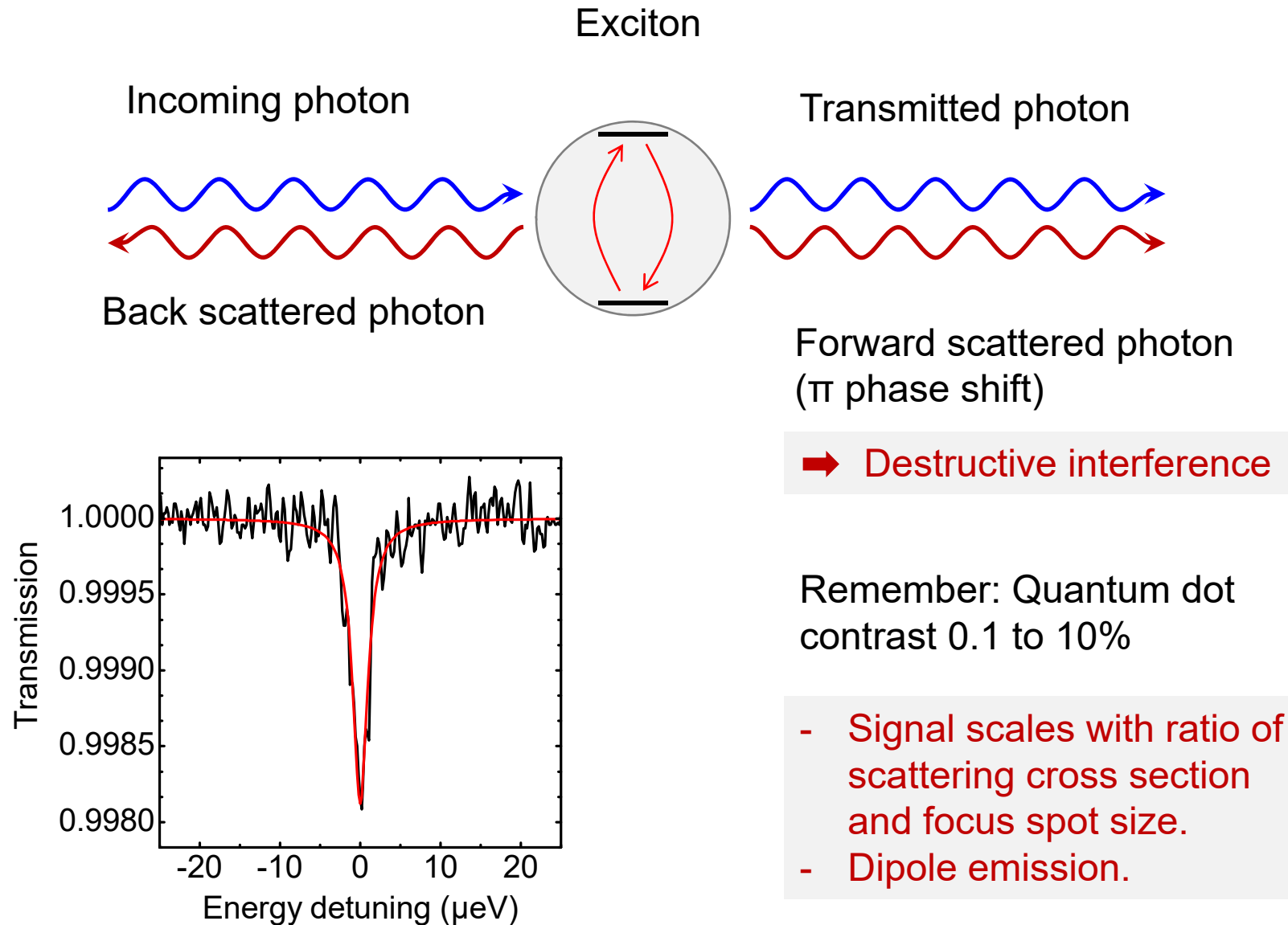
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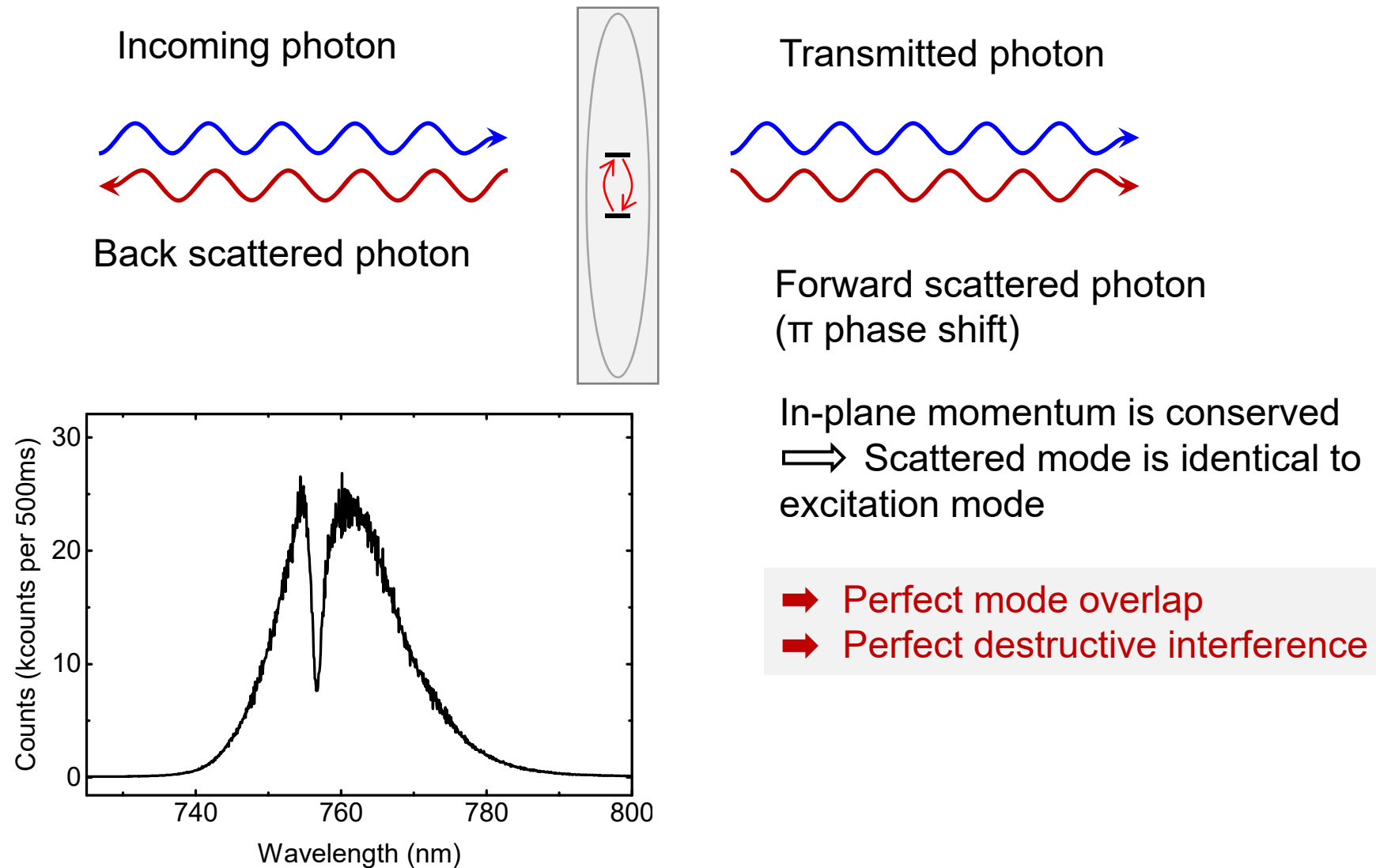


Optical Response of an Exciton



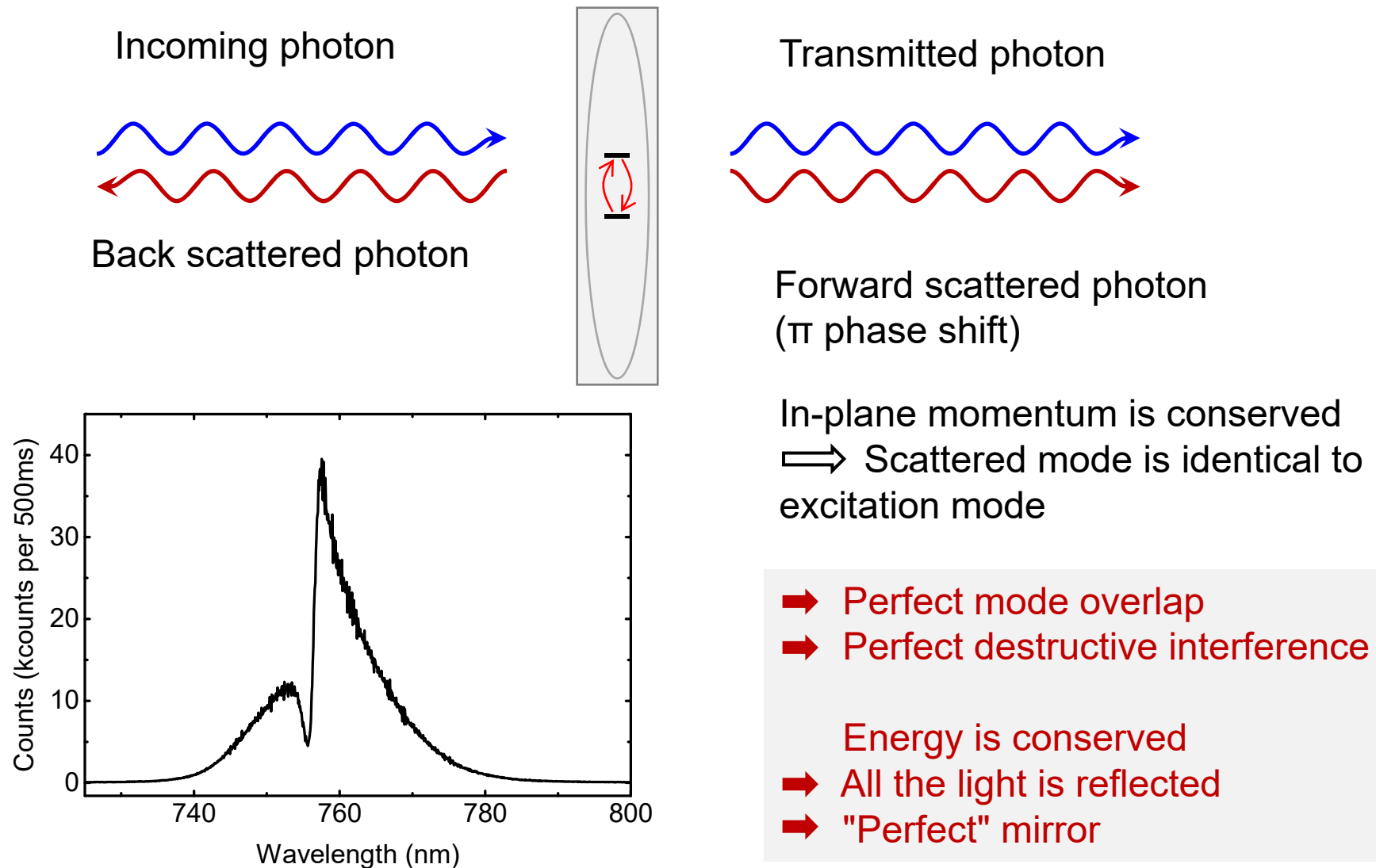
Optical Response of a 2D Exciton

2D Exciton



The "Perfect" Mirror

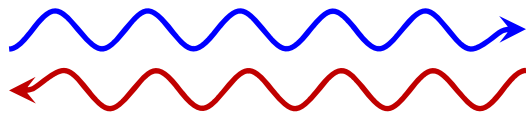
2D Exciton



The “Perfect” Mirror

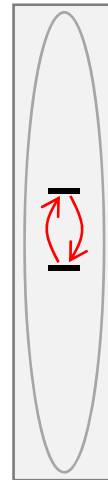
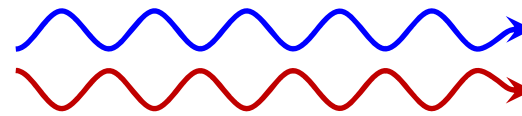
2D Exciton

Incoming photon

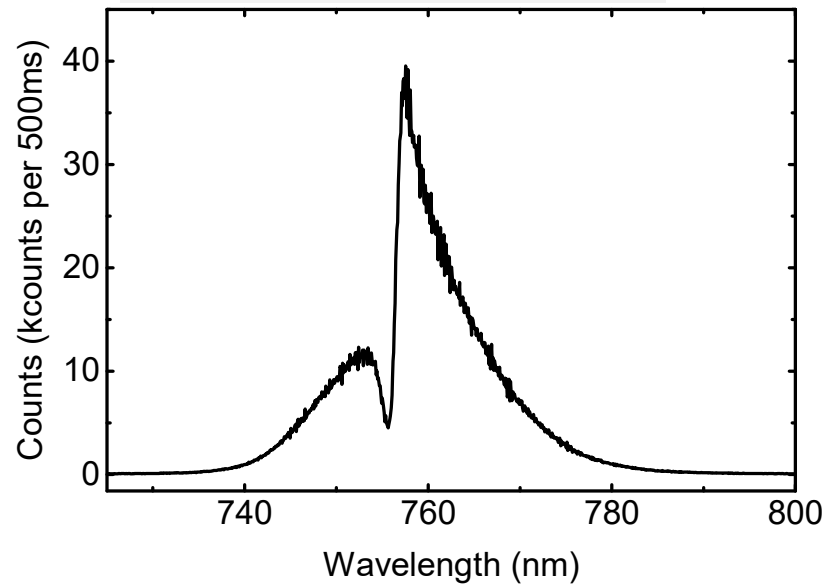


Back scattered photon

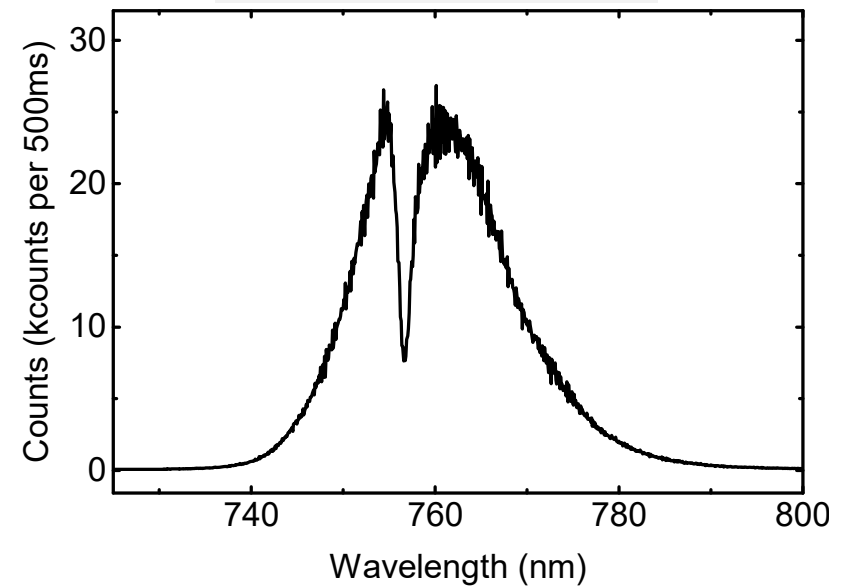
Transmitted photon



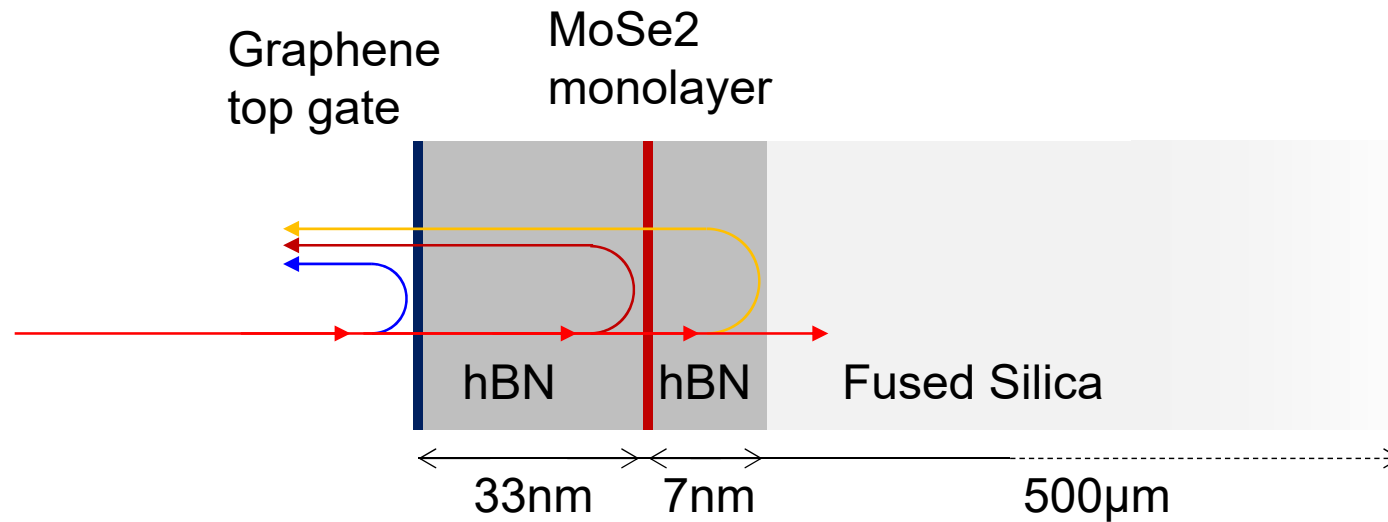
Asymmetric resonance



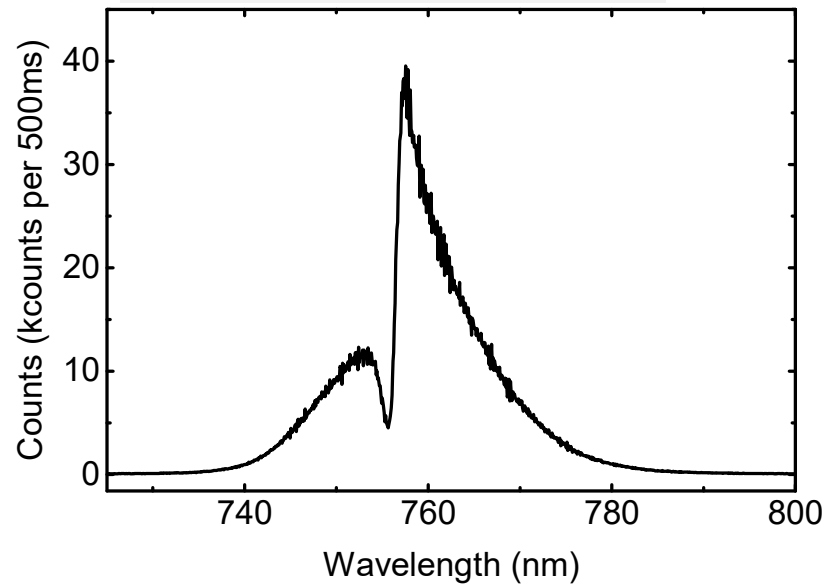
Finite transmission



The Perfect Mirror

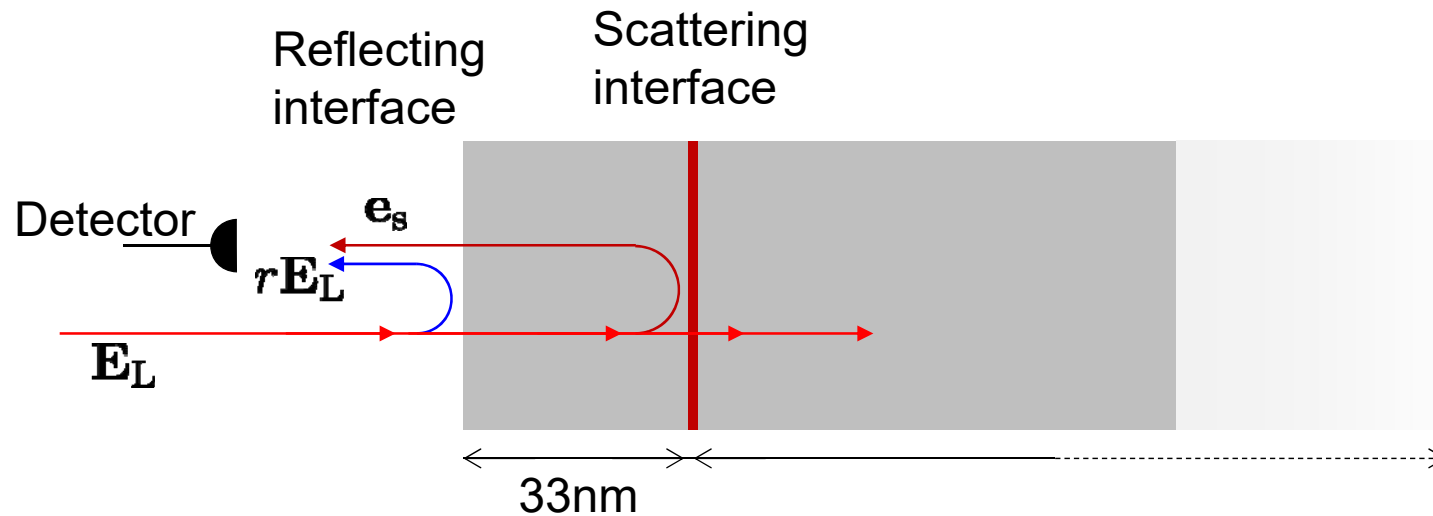


Asymmetric resonance



- Interference between light reflected from
- Vacuum – hBN interface
 - MoSe₂ monolayer
 - hBN – Fused Silica substrate

Reflection Spectrum



Coherently scattered field: $\mathbf{e}_s = \mathbf{E}_L \frac{\delta\gamma + i\gamma^2}{\delta^2 + \gamma^2}$

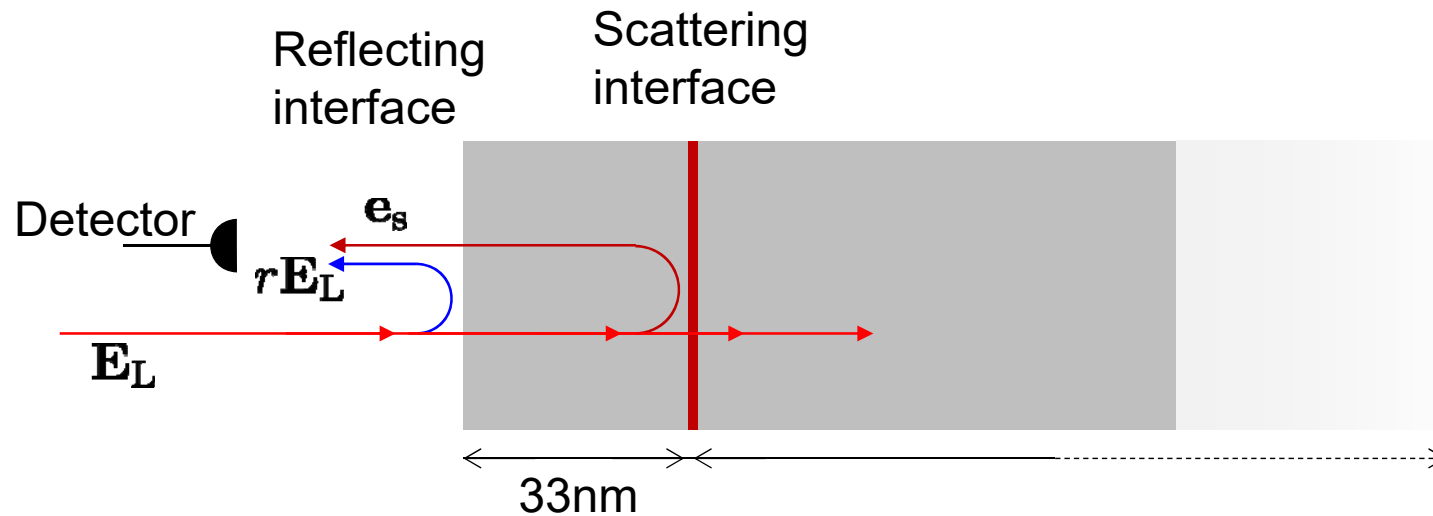
Reflected field: $\Delta R = |r\mathbf{E}_L + \mathbf{e}_s|^2 = |r\mathbf{E}_L|^2 + 2r\mathbf{e}_s\mathbf{E}_L + |\mathbf{e}_s|^2$

Interference term: $\Delta R_I = 2r\mathbf{e}_s\mathbf{E}_L$

Path length difference between $r\mathbf{E}_L$ and $\mathbf{e}_s$ on the detector: $L = 2 \times 33\text{nm}$

$\Rightarrow$ Phase shift: $\phi = \frac{2L}{\lambda} 2\pi$

Reflection Spectrum

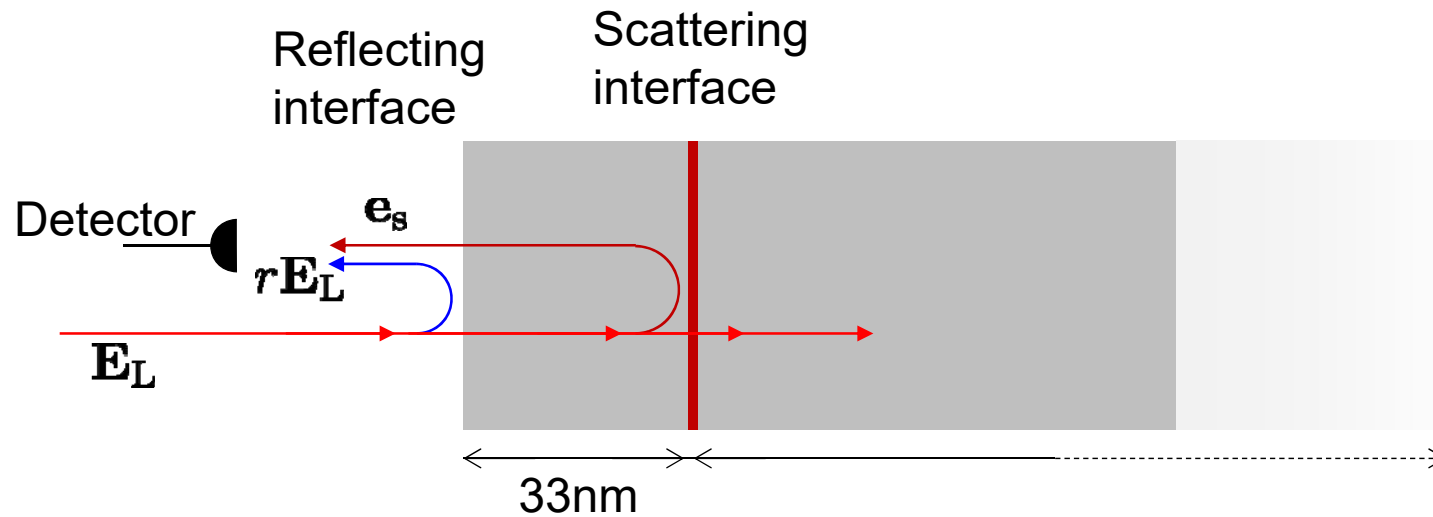


Coherently scattered field: $\mathbf{e}_s = \mathbf{E}_L \frac{\delta\gamma + i\gamma^2}{\delta^2 + \gamma^2}$

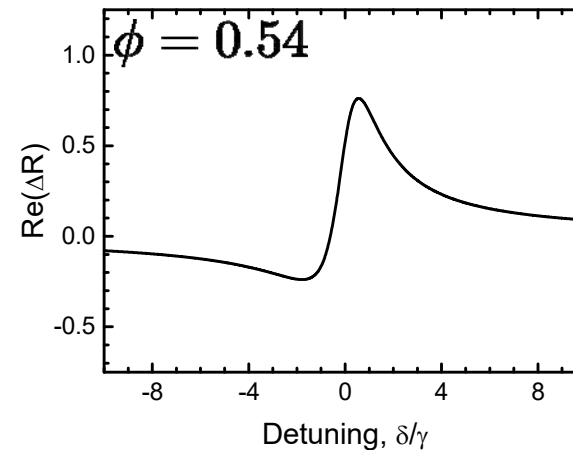
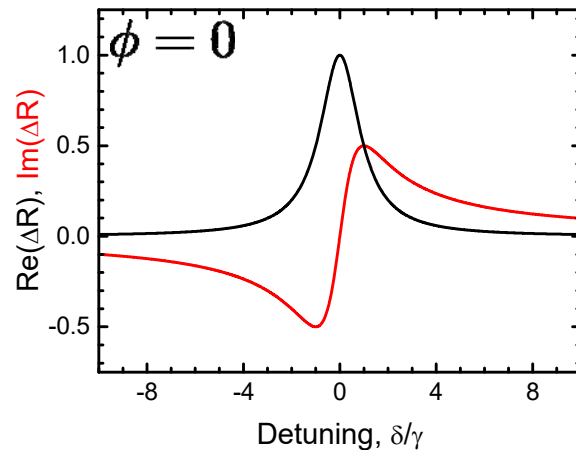
Contribution of the interference term on the detector
(only the real part):

$$\Delta R_I = 2r\mathbf{e}_s\mathbf{E}_L = 2re^{i\phi} \frac{\delta\gamma + i\gamma^2}{\delta^2 + \gamma^2} = (\delta\gamma \cos(\phi) - \gamma^2 \sin(\phi)) \frac{1}{\delta^2 + \gamma^2}$$

Reflection Spectrum



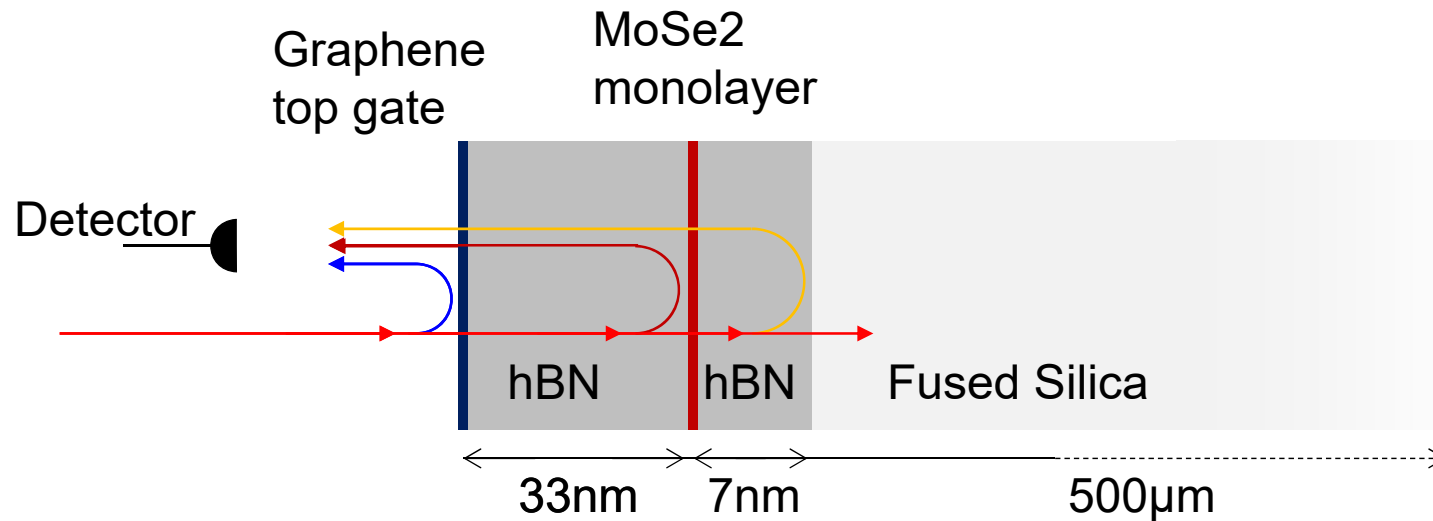
$$\Delta R_I = 2r\mathbf{e}_s\mathbf{E}_L = 2re^{i\phi} \frac{\delta\gamma + i\gamma^2}{\delta^2 + \gamma^2} = (\delta\gamma \cos(\phi) - \gamma^2 \sin(\phi)) \frac{1}{\delta^2 + \gamma^2}$$



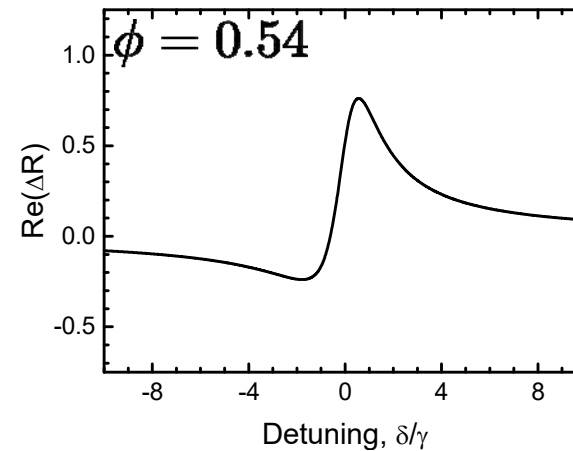
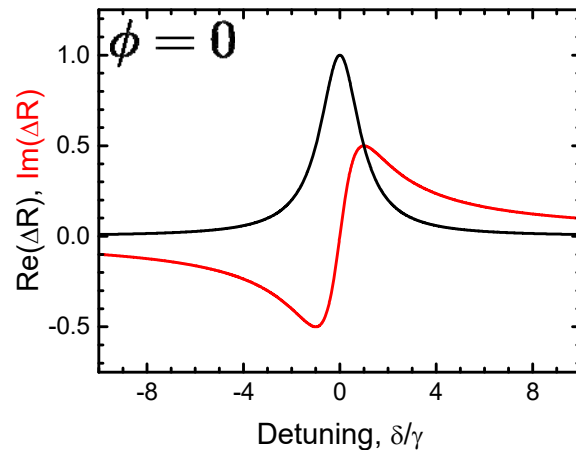
Knowing all thicknesses and refractive indices:

⇒ Calculate normalized transmission and reflection spectra

Reflection Spectrum



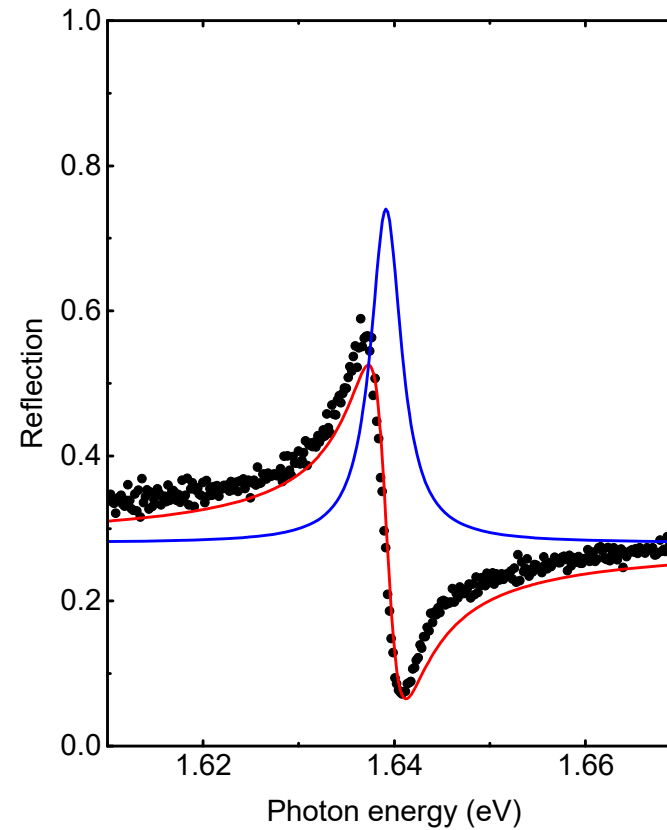
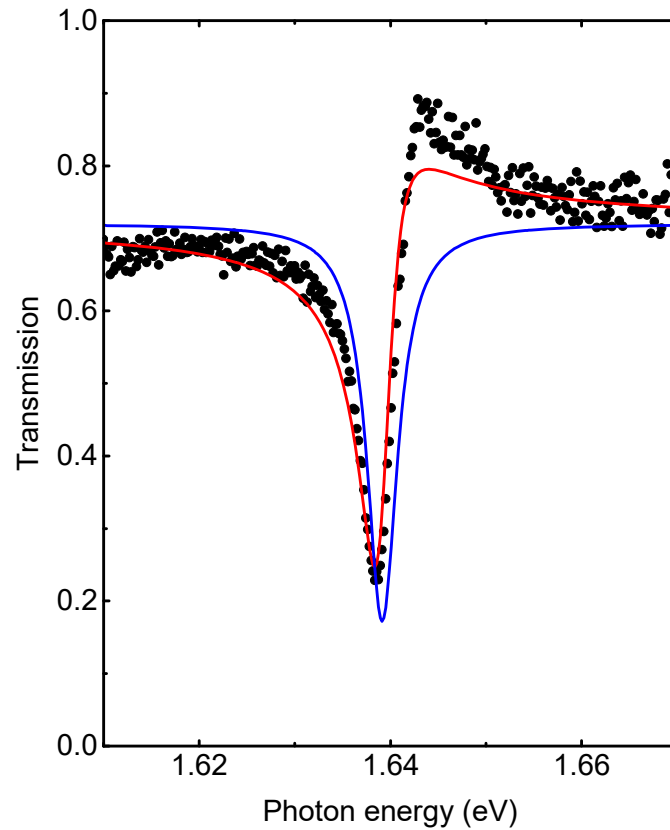
$$\Delta R_I = 2re_s \mathbf{E}_L = 2re^{i\phi} \frac{\delta\gamma + i\gamma^2}{\delta^2 + \gamma^2} = (\delta\gamma \cos(\phi) - \gamma^2 \sin(\phi)) \frac{1}{\delta^2 + \gamma^2}$$



Knowing all thicknesses and refractive indices:

⇒ Calculate normalized transmission and reflection spectra

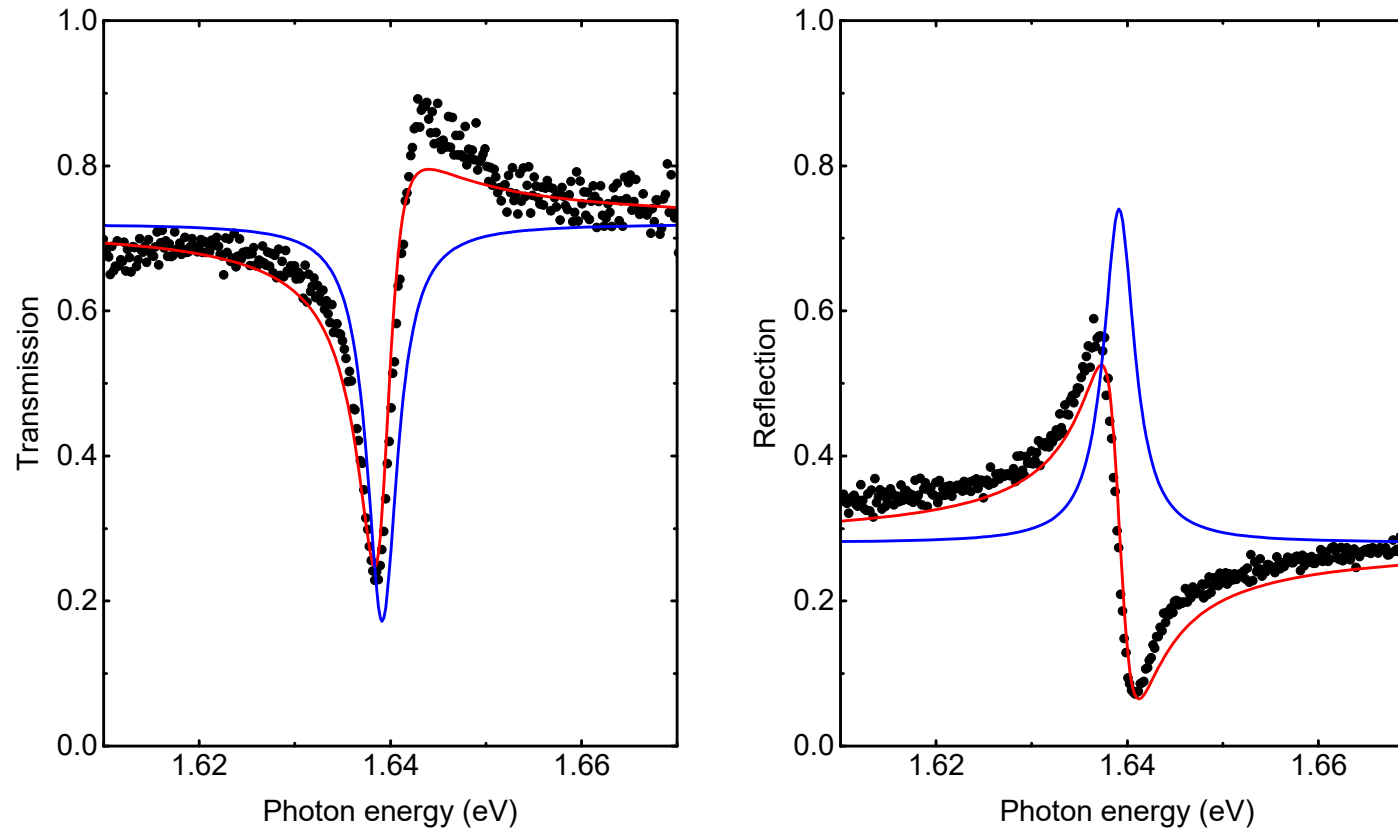
An Atomically Thin Mirror



Knowing all thicknesses and refractive indices:

⇒ Calculate normalized transmission and reflection spectra

An Atomically Thin Mirror



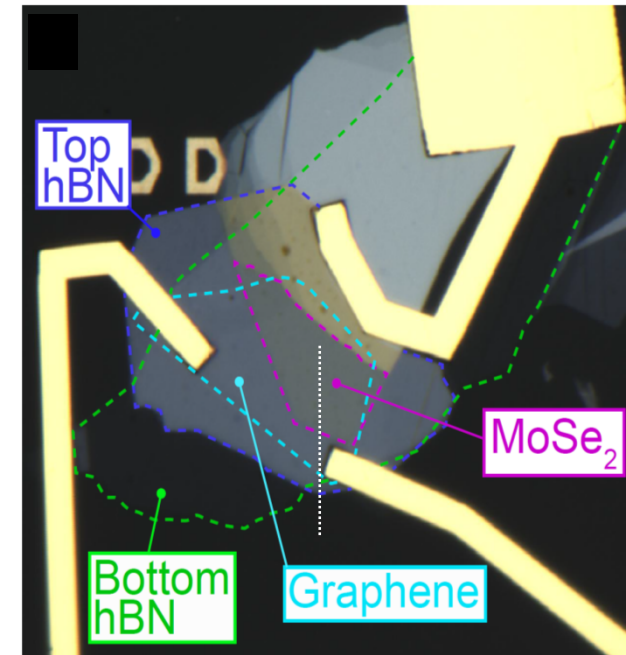
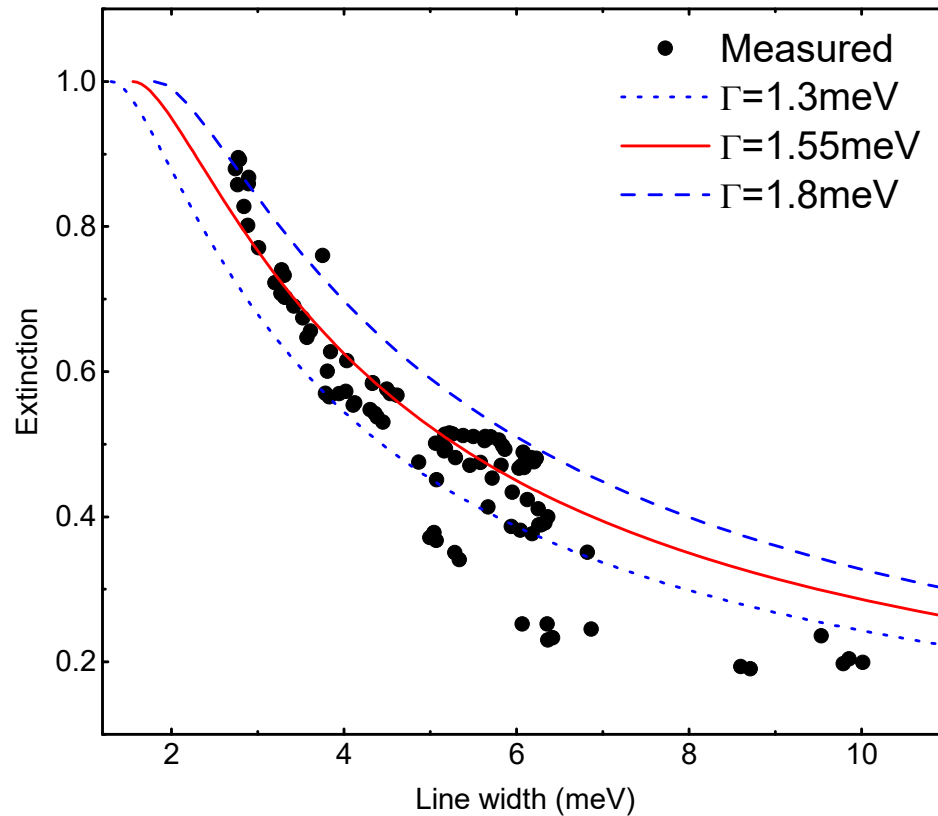
Maximum extinction: 76%

Maximum reflection: 46%

Limited by inhomogeneous broadening (disorder).

Disorder on sample leads to shifts in resonance and fluctuations in line width.

Influence of Disorder



Extinction:

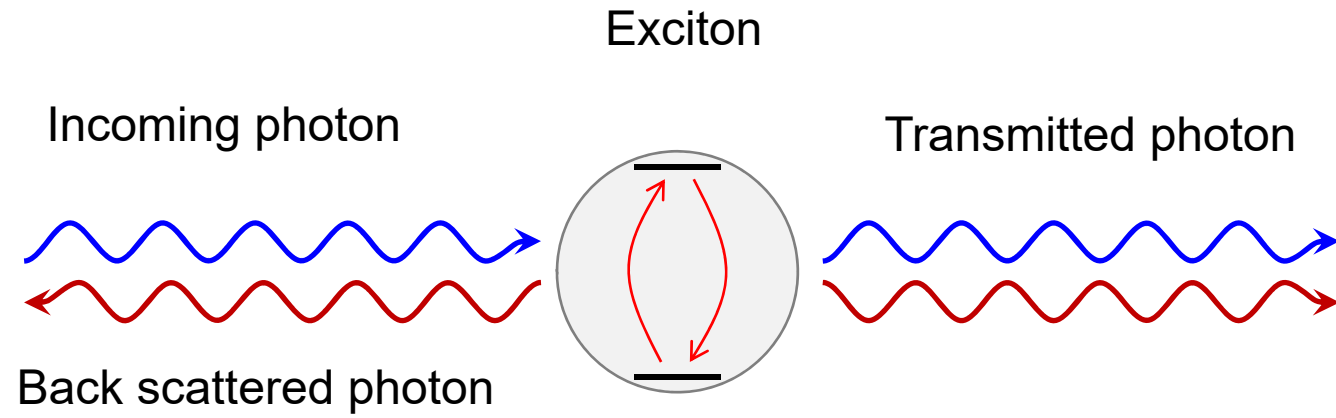
$$1 - T_{\min} = 1 - \frac{(\gamma_{\text{tot}} - \Gamma)^2}{\gamma_{\text{tot}}^2}$$

Extrapolation of line with to $\Gamma=1.3\text{-}1.8\text{meV}$

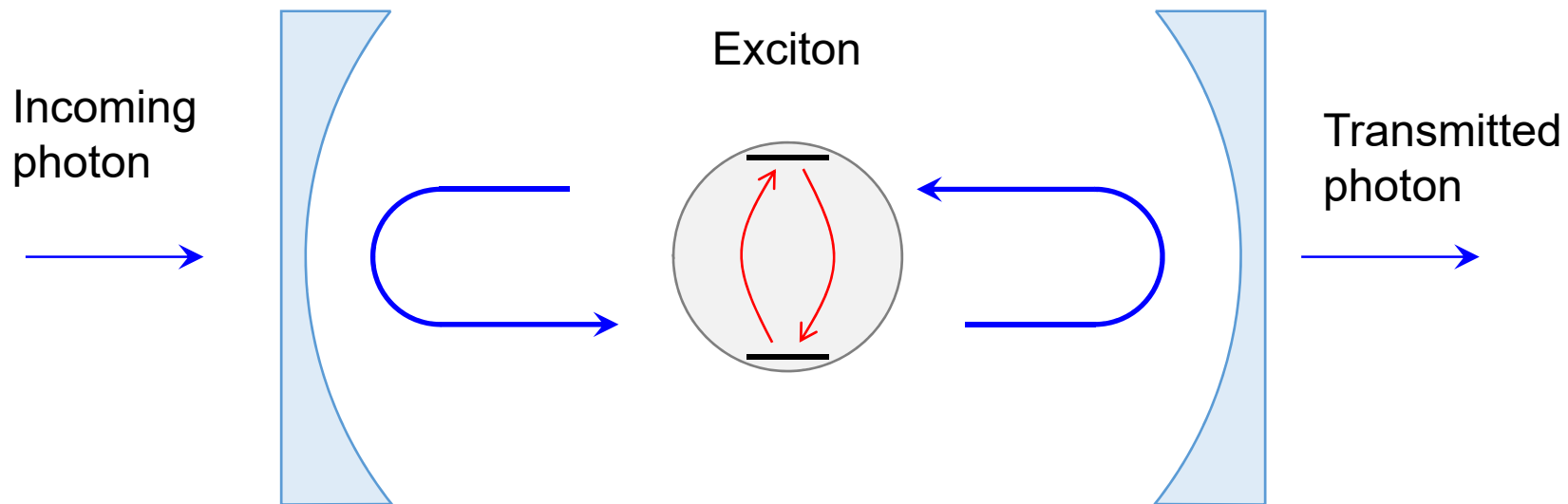
Limited by inhomogeneous broadening (disorder).

Disorder on sample leads to shifts in resonance and fluctuations in line width.

Cavity Quantum Electrodynamics



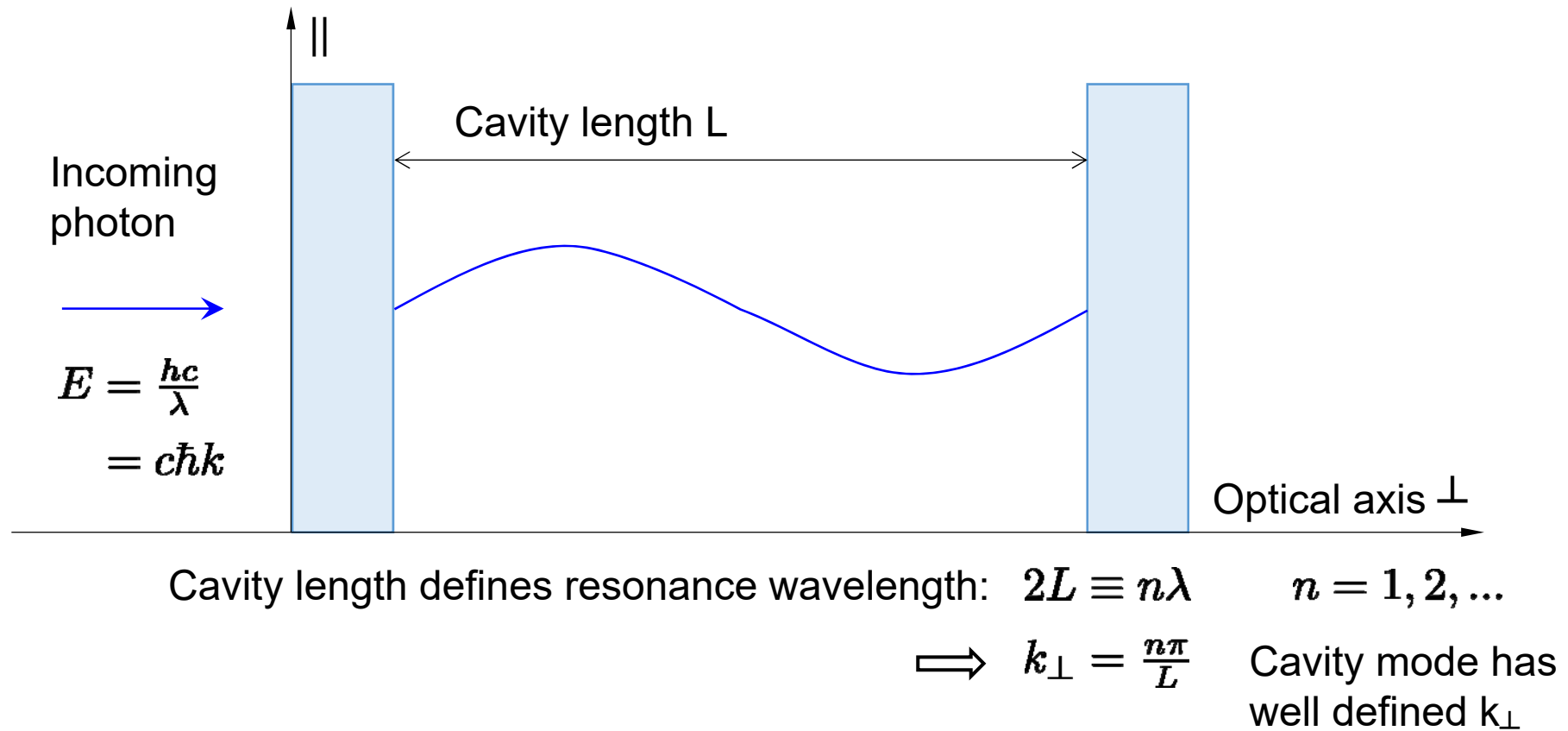
Cavity Quantum Electrodynamics



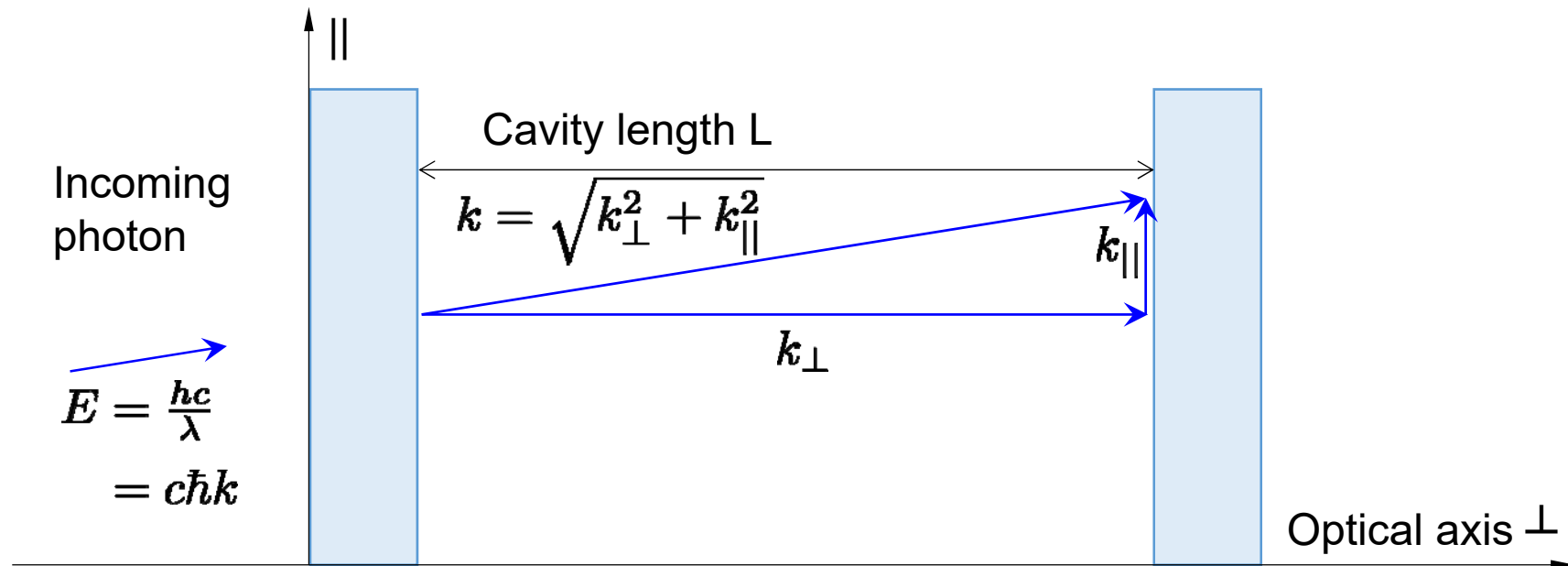
Confine photon to cavity mode

Photon can be scattered by the exciton multiple times

Planar 2D Cavity



Planar 2D Cavity



Cavity length defines resonance wavelength: $2L \equiv n\lambda \quad n = 1, 2, \dots$

In general:

$$\Rightarrow k_{\perp} = \frac{n\pi}{L} \quad \text{Cavity mode has well defined } k_{\perp}$$

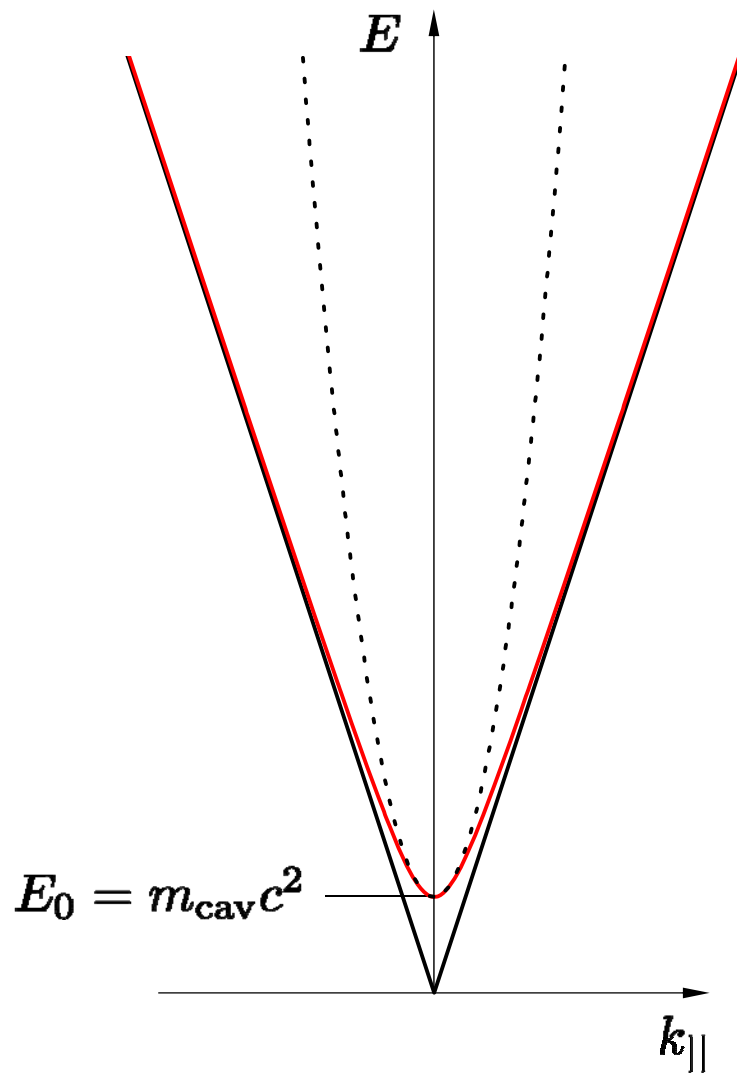
Energy of a cavity photon: $E = \hbar\omega = c\hbar k = c\hbar \sqrt{k_{\perp}^2 + k_{\parallel}^2}$

$$(\hbar\omega)^2 = \left(\frac{n\pi\hbar}{Lc}c^2\right)^2 + (\hbar ck_{\parallel})^2$$

With: $m_{\text{cav}} = \frac{n\pi\hbar}{Lc}$

$$\hbar\omega \approx m_{\text{cav}}c^2 + \frac{\hbar^2 k_{\parallel}^2}{2m_{\text{cav}}}$$

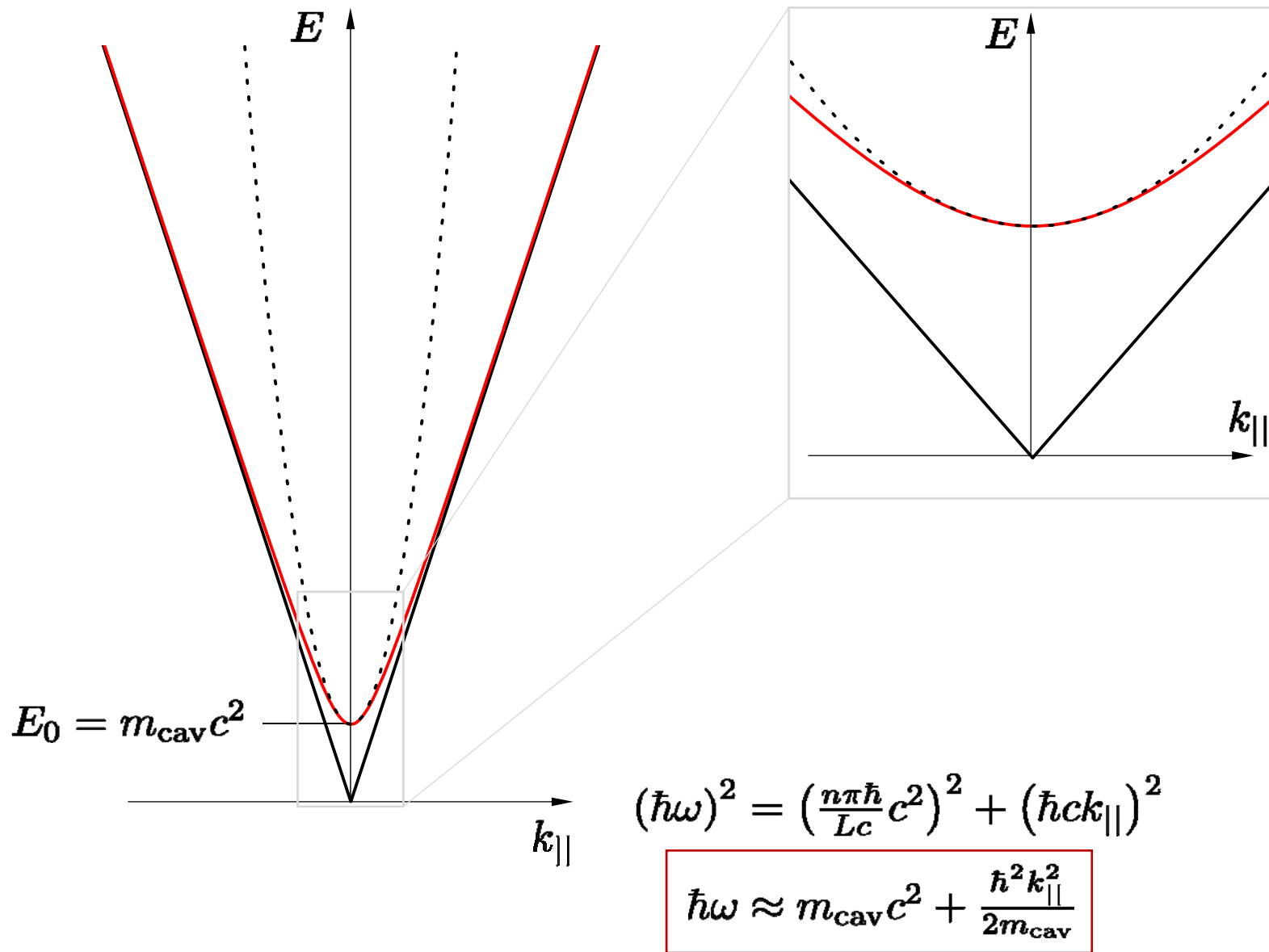
Cavity Dispersion



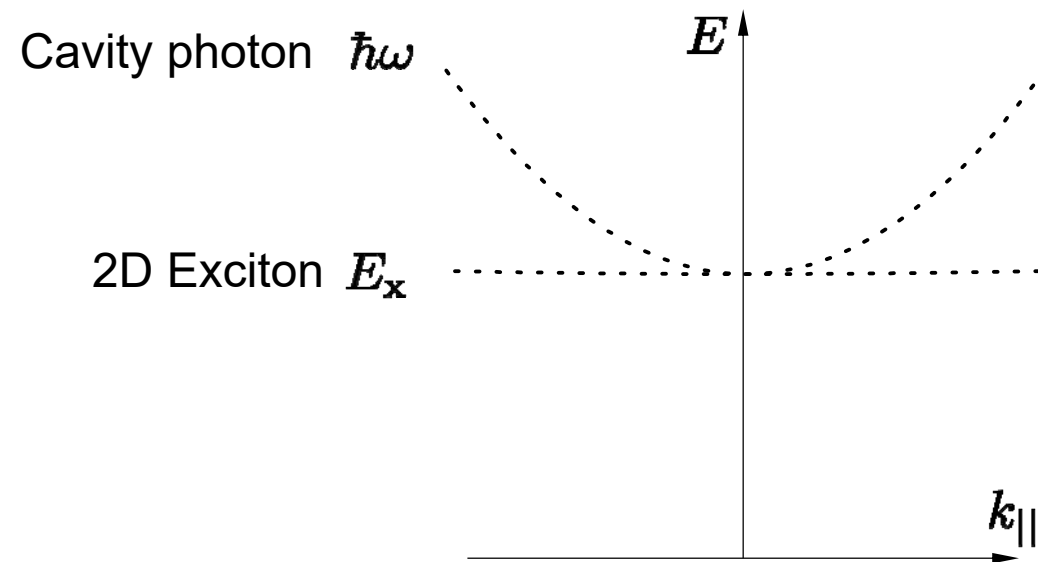
$$(\hbar\omega)^2 = \left(\frac{n\pi\hbar}{Lc}c^2\right)^2 + (\hbar ck_{||})^2$$

$$\hbar\omega \approx m_{\text{cav}}c^2 + \frac{\hbar^2 k_{||}^2}{2m_{\text{cav}}}$$

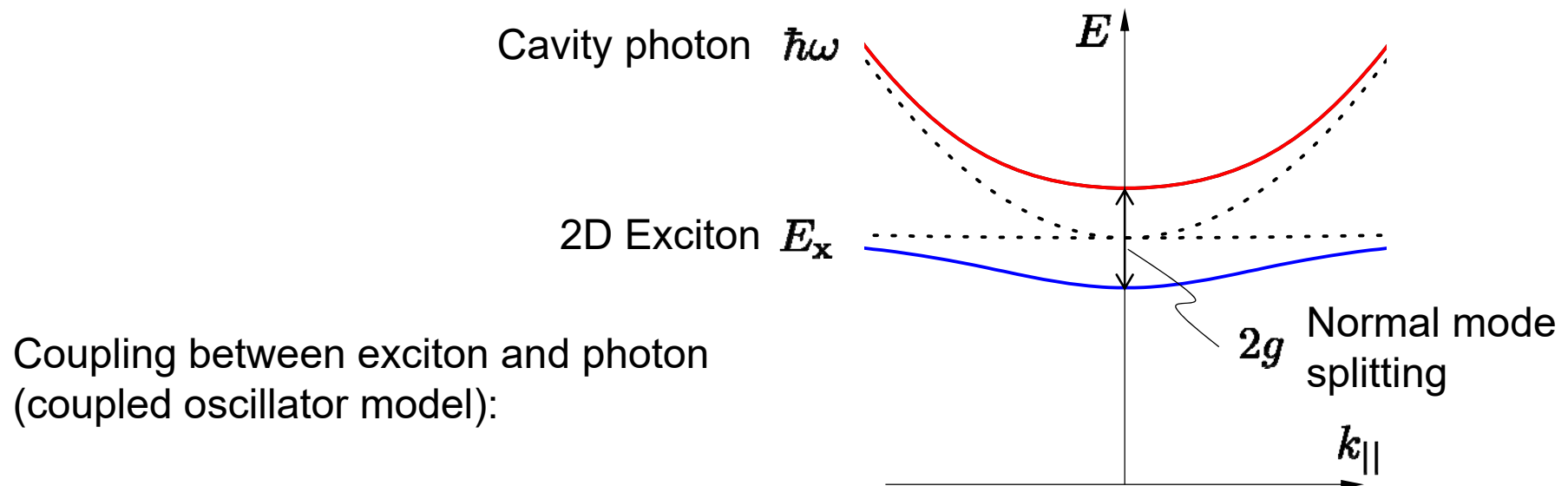
Cavity Dispersion



Cavity Mode Coupled to 2D Exciton



Cavity Mode Coupled to 2D Exciton



$$\hat{H} = \begin{pmatrix} \hbar\omega & g \\ g & E_x \end{pmatrix}$$

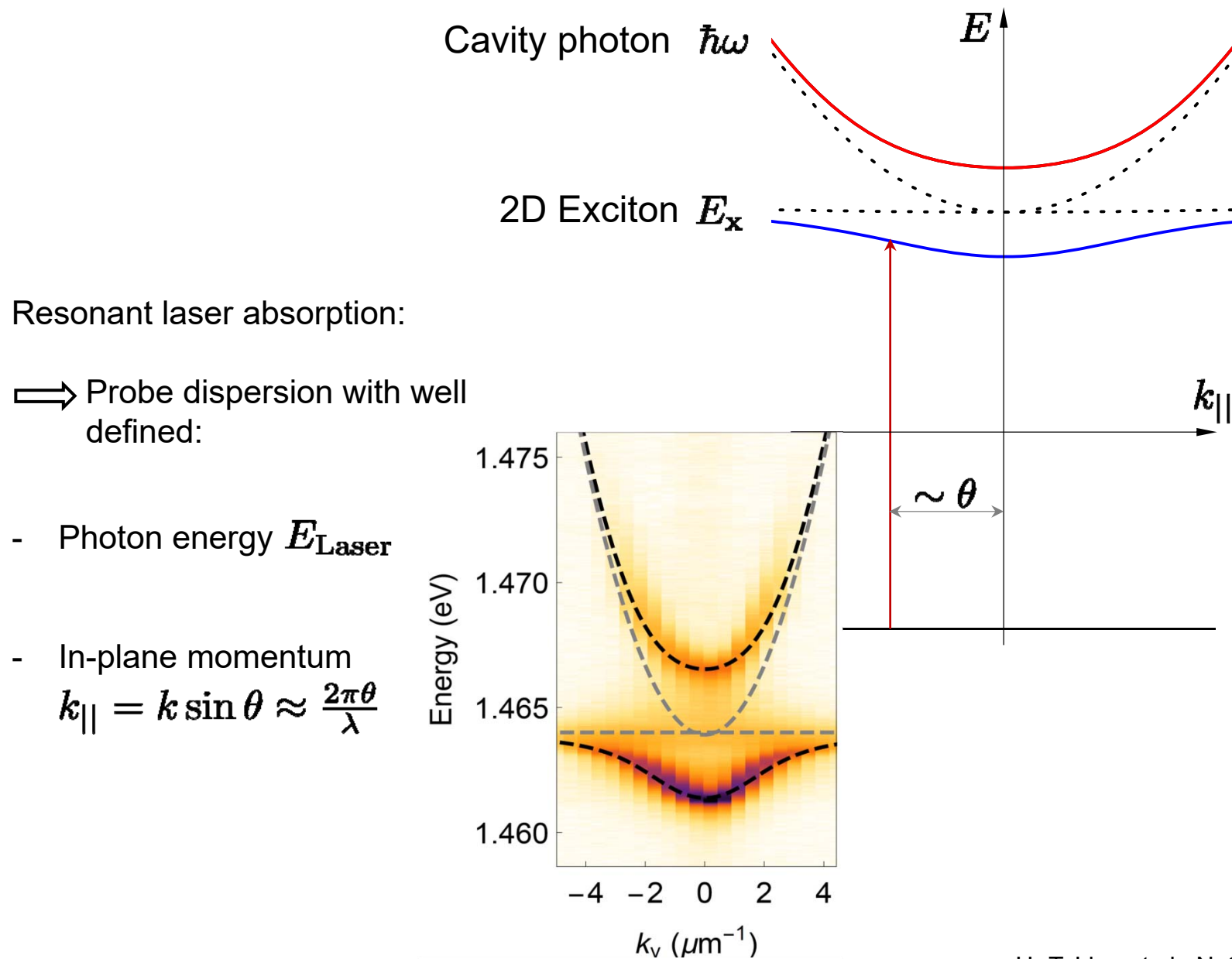
Coupling constant g

New eigenmodes:

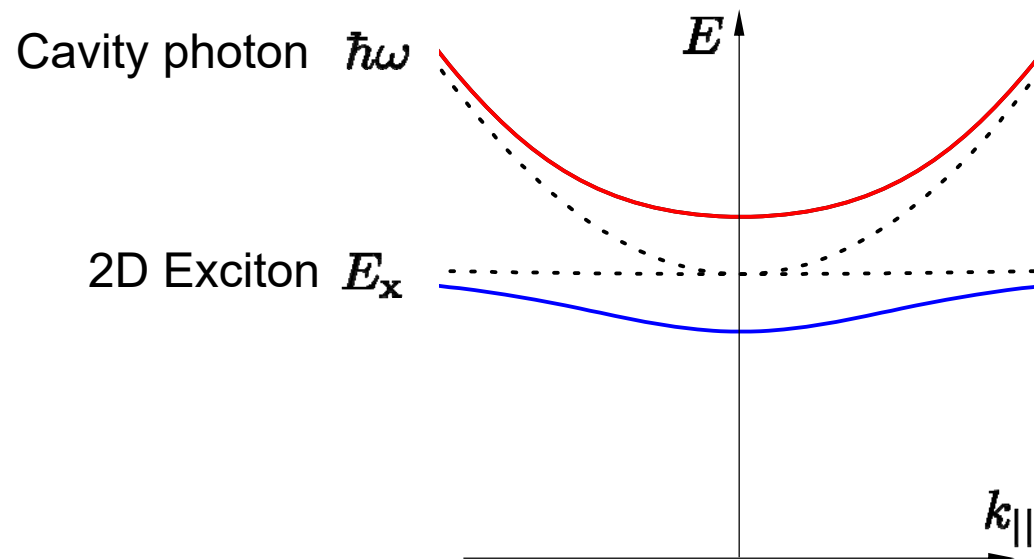
$$E_{\pm} = \frac{1}{2} \left(\hbar\omega + E_x \pm \sqrt{4g^2 + (\hbar\omega - E_x)^2} \right)$$

$E_+ \equiv$ Upper polariton
 $E_- \equiv$ Lower polariton

Cavity Mode Coupled to 2D Exciton



Cavity Mode Coupled to 2D Exciton



Lower polariton:

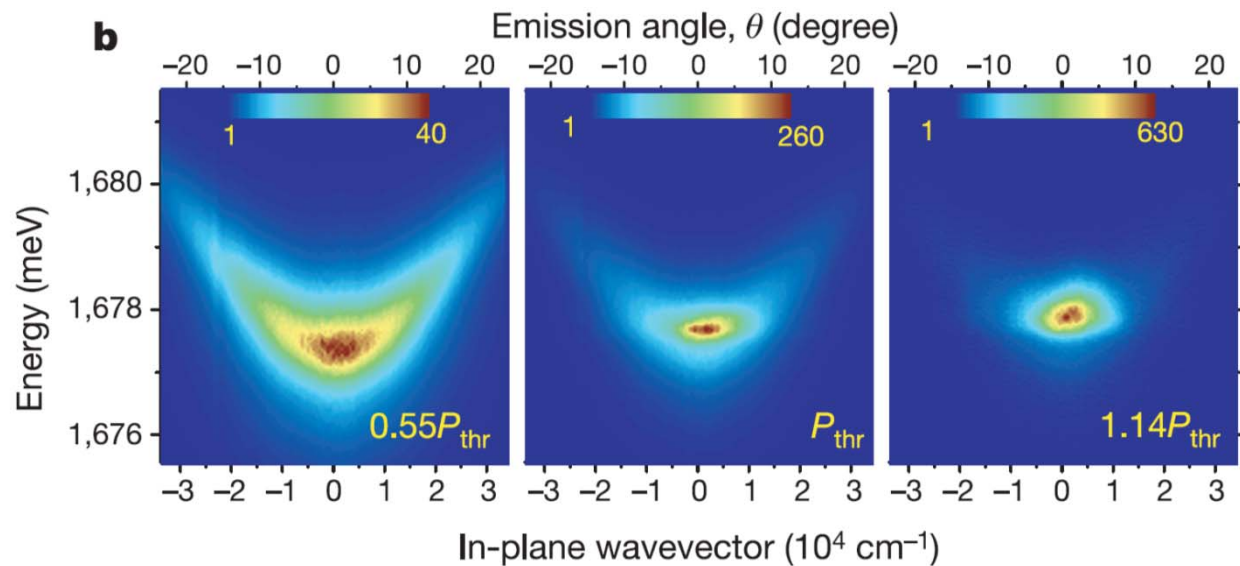
Lower mass than exciton

$$m_{\text{cav}} \approx 1 \times 10^{-5} m_e$$

At resonance: $\frac{1}{m_{\text{pol}}} = \frac{1}{2m_{\text{cav}}}$

⇒ Bose-Einstein condensation of polaritons. (up to room temperature)

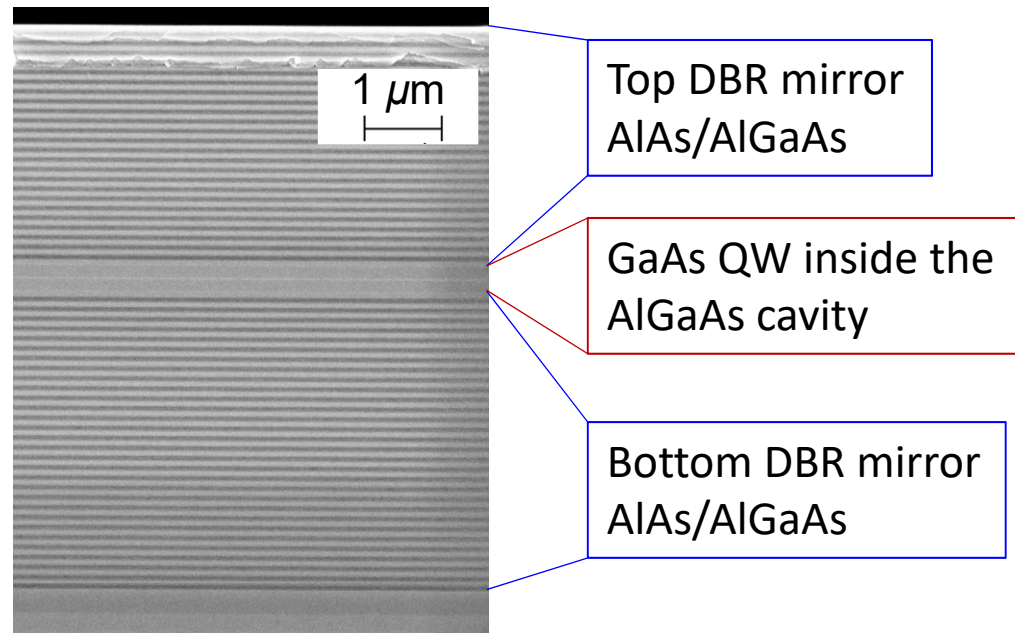
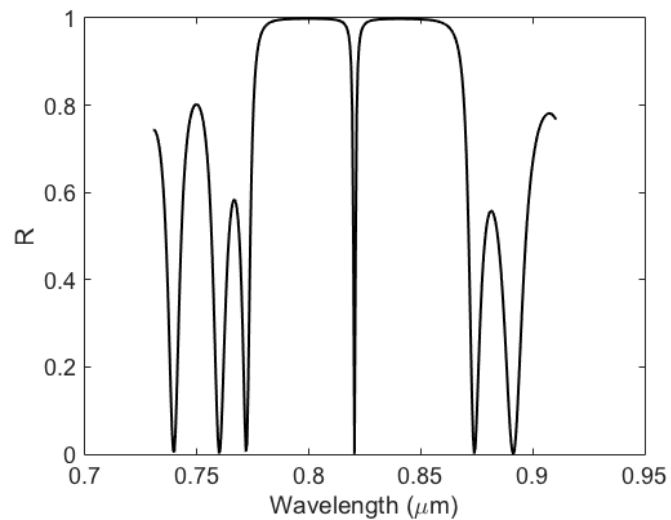
$$T_c \sim \frac{1}{m}$$



2D Polaritons

Example: Epitaxially grown planar microcavity

Reflection spectrum of a cavity with Bragg mirrors:

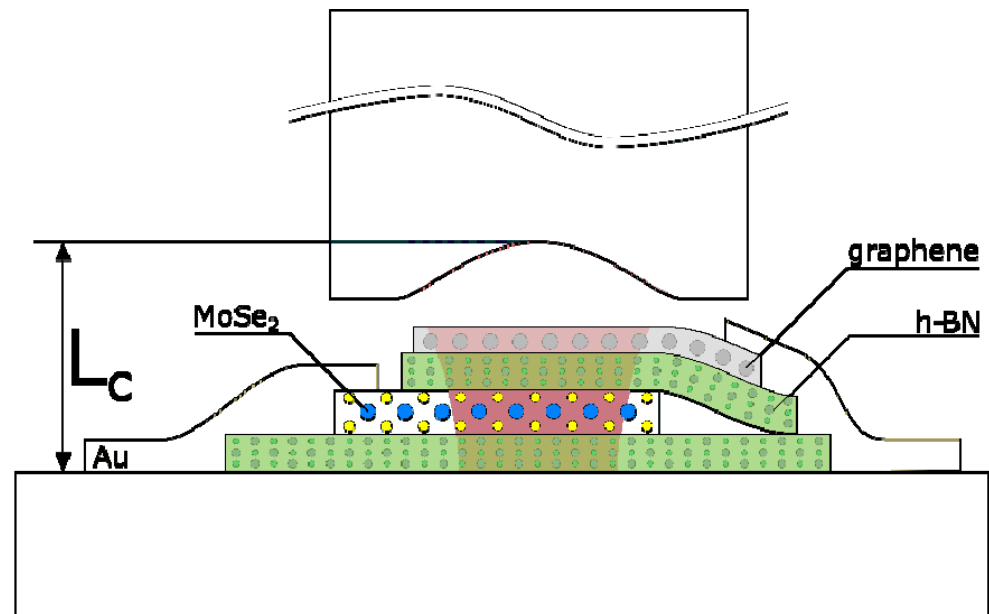


Cross section SEM image

High quality, versatile, robust micro cavity
Basis for most quantum photonic devices.

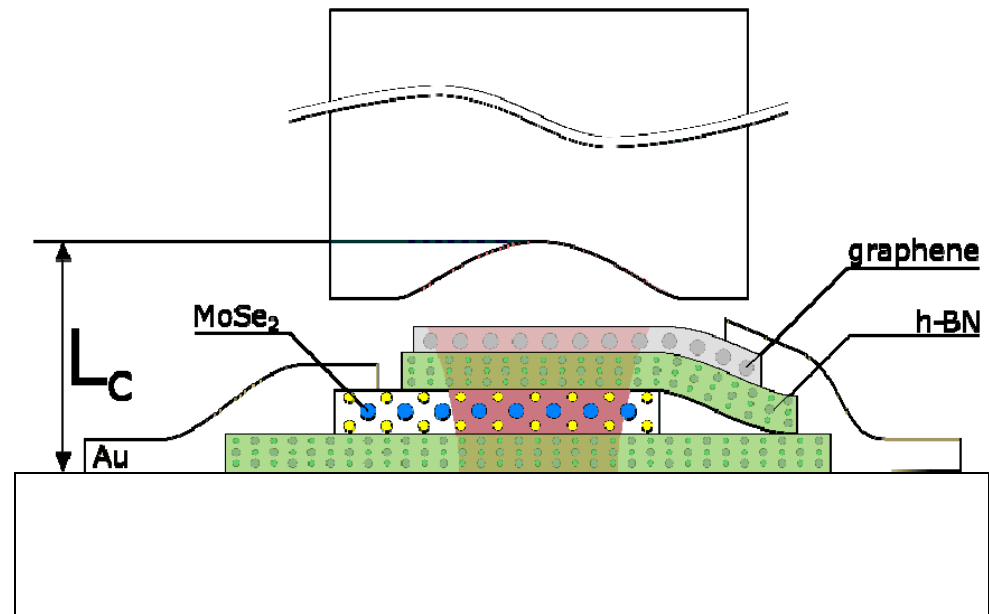
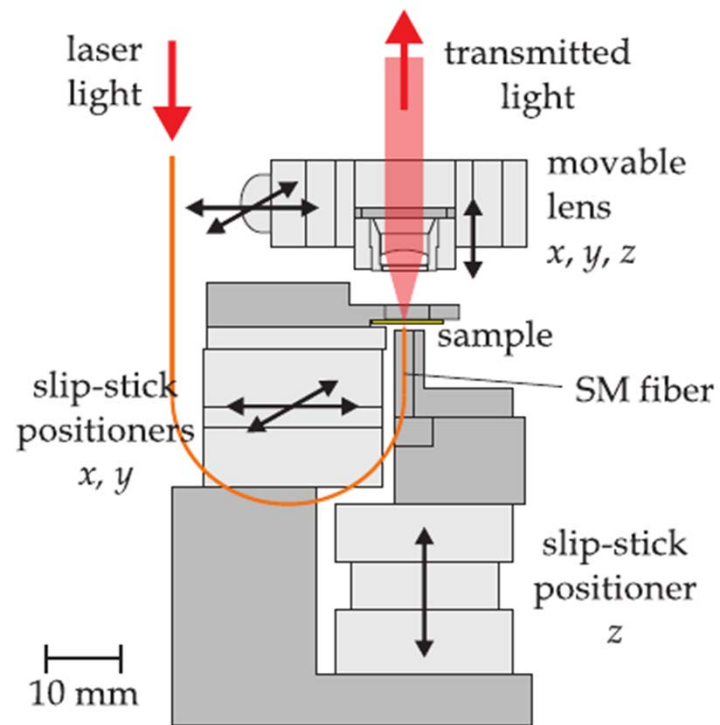
TMD Coupled to a 0D Cavity Mode

Open optical-fiber based cavity setup:



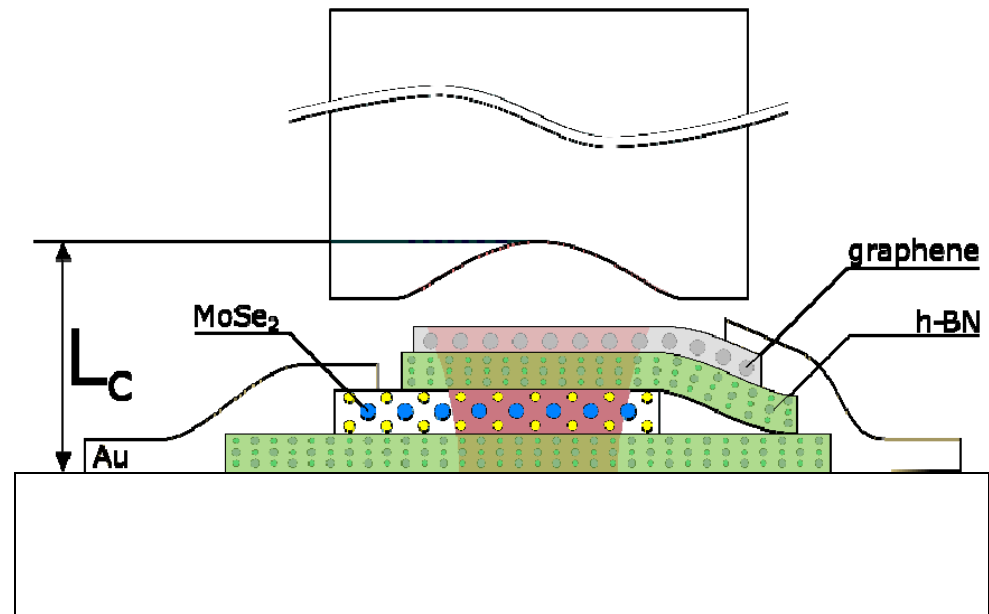
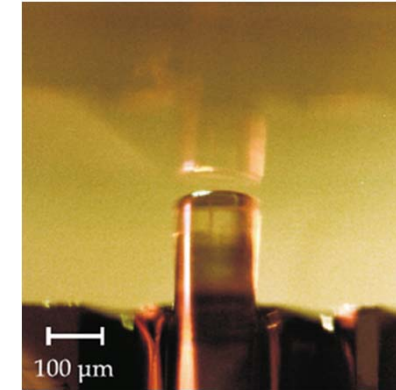
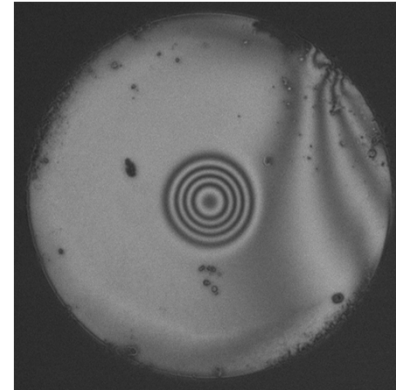
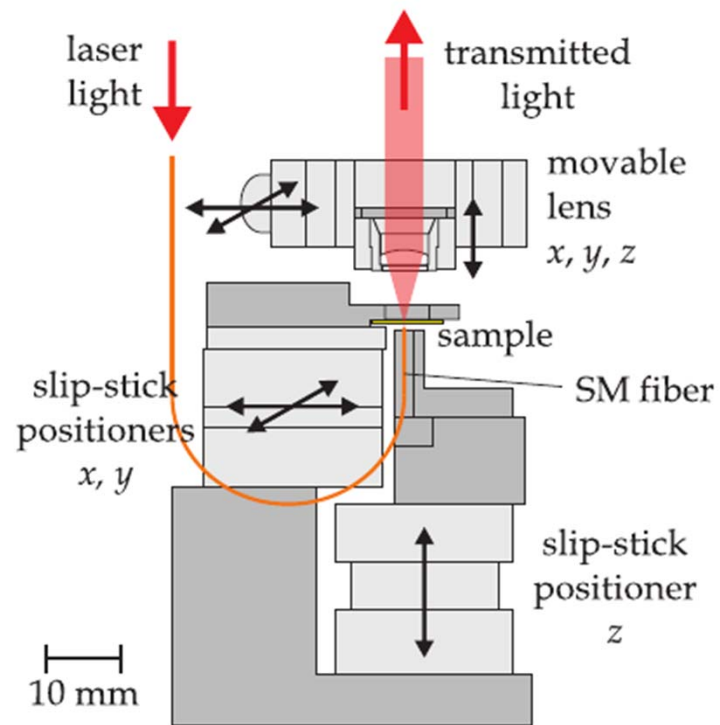
TMD Coupled to a 0D Cavity Mode

Open optical-fiber based cavity setup:



TMD Coupled to a 0D Cavity Mode

Open optical-fiber based cavity setup:

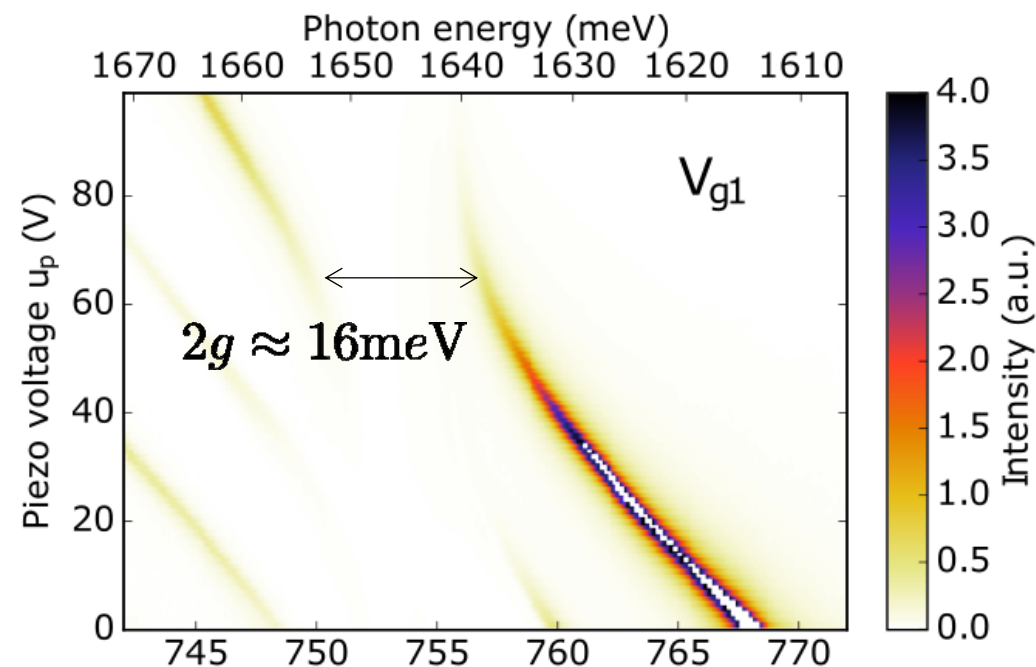


Strong Coupling of a TMD Exciton to a 0D Cavity Mode

Open optical-fiber based cavity setup:

- Scan cavity mode to sample position
- Tune cavity length

Transmission spectrum as function of cavity length:

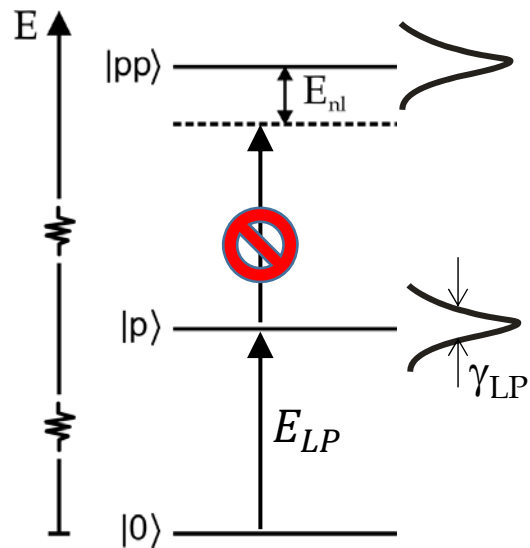


Normal mode splitting: Direct measurement of light matter coupling

Single Photon Interactions

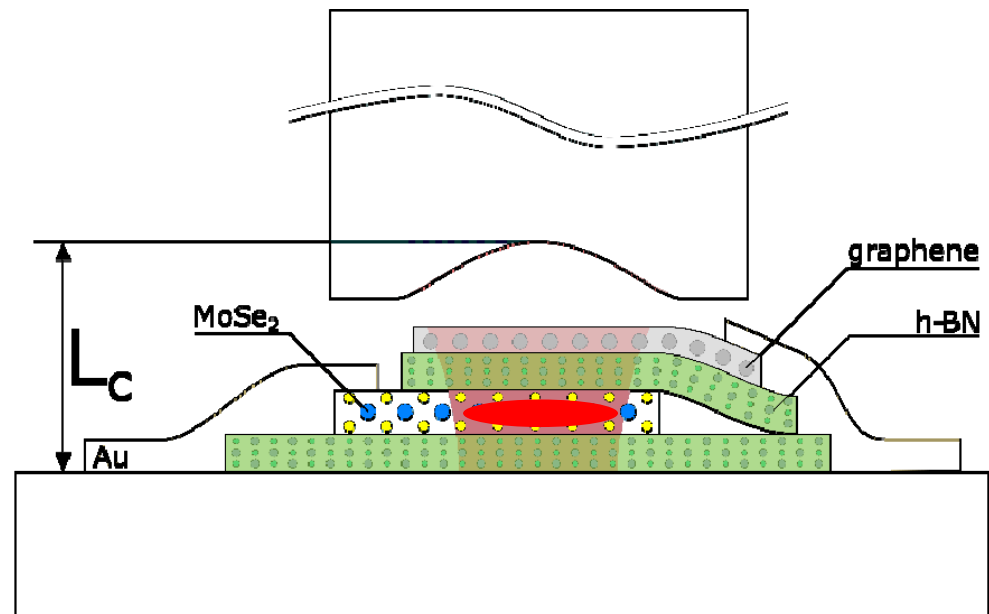
0D Cavity mode

⇒ confined polariton state



Interactions $>$ Linewidth

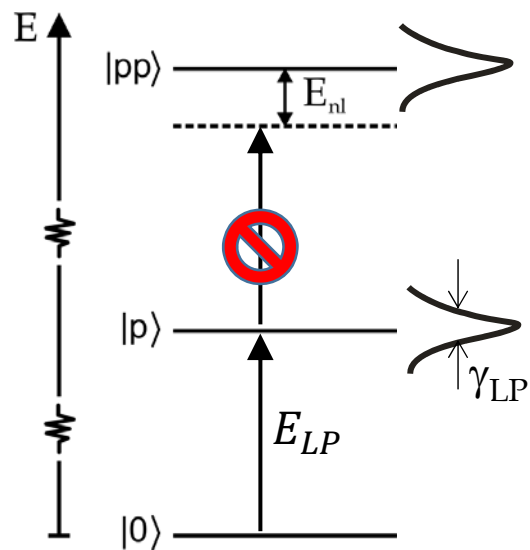
⇒ Second polariton can not be created resonantly



Single Photon Interactions

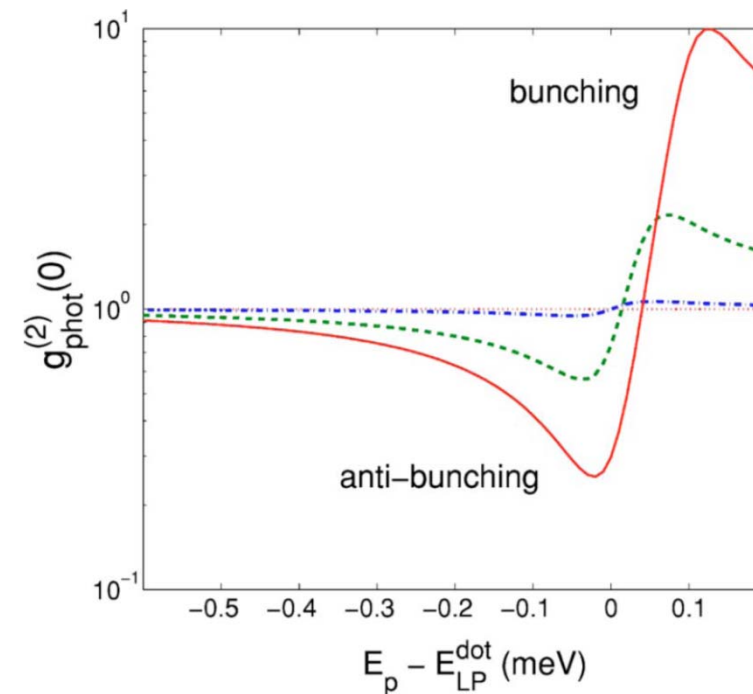
0D Cavity mode

⇒ confined polariton state



Interactions > Linewidth

⇒ Second polariton can not be created resonantly



Experimental signature:
Non classical light emission – anti bunching